

# An Introduction to Computational Nanoscience

Lin-Wang Wang

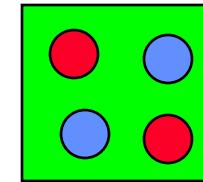
Material Science Division  
Lawrence Berkeley National Lab

US Department of Energy  
Office of Science

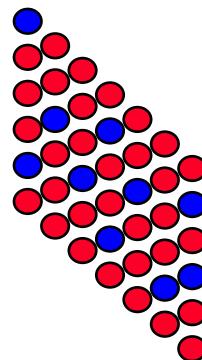
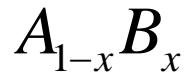
- What can we do ?
- How do we do it ?
- Examples

# Making new solid state materials

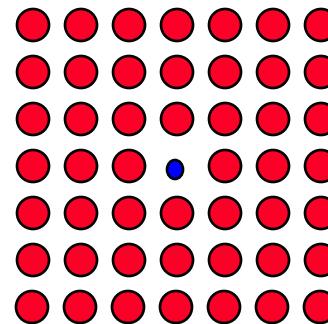
- New crystal compounds



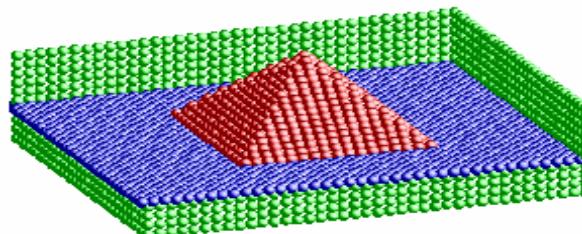
- Alloys



- Impurity and doping



- Modifying the size and shape of the material

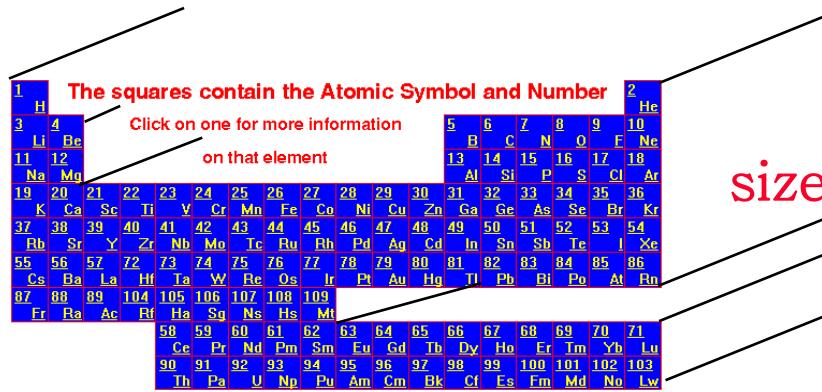


# Nanostructure as a new material

**Definition:** Nanostructure is an assembly of nanometer scale “building blocks”.



**Why nanometer scale:** This is the scale when the properties of these “building blocks” become different from bulk.

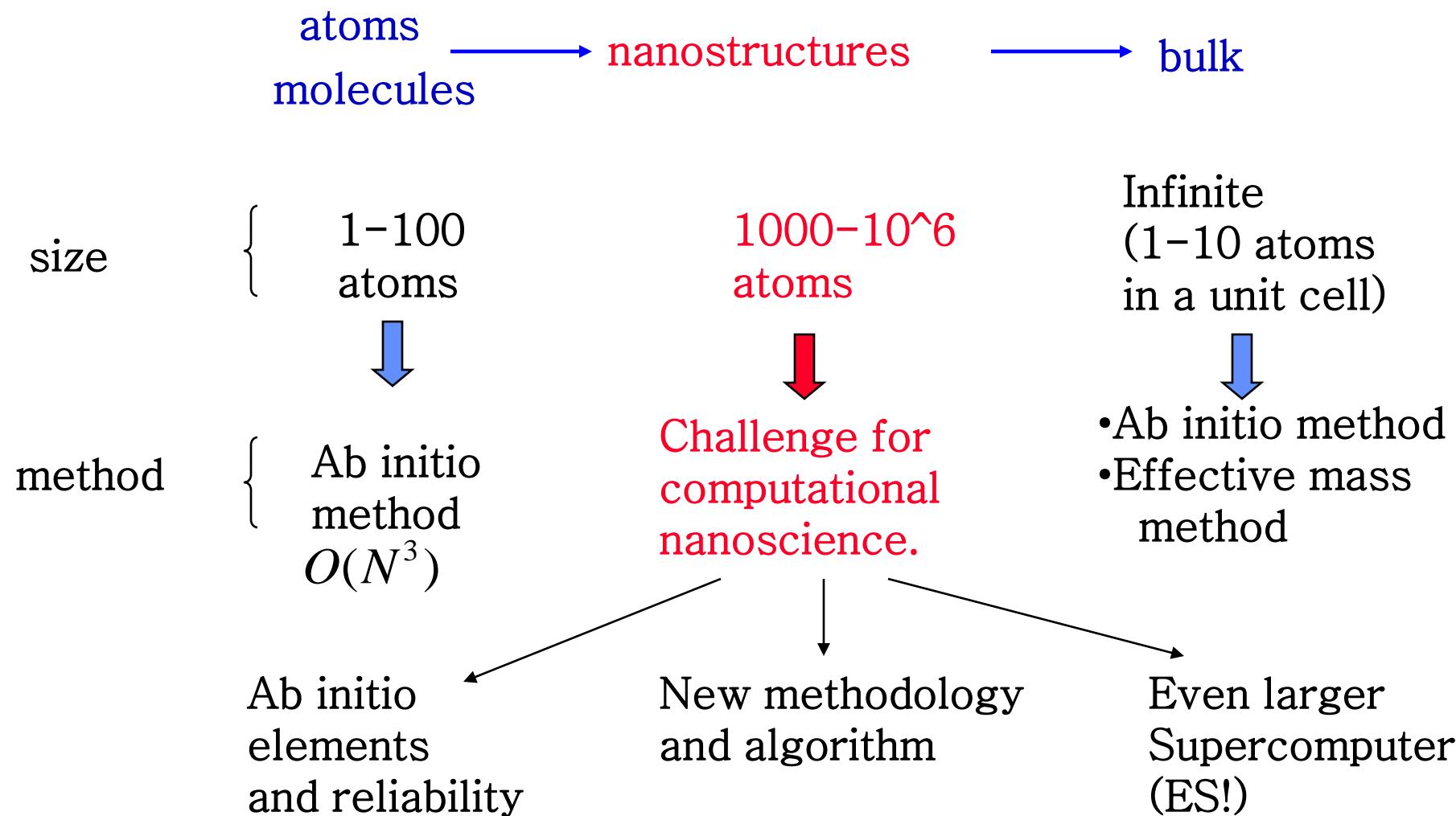


Nanostructure

Electron Wavefunction

Both are in nanometers

# Computational challenge

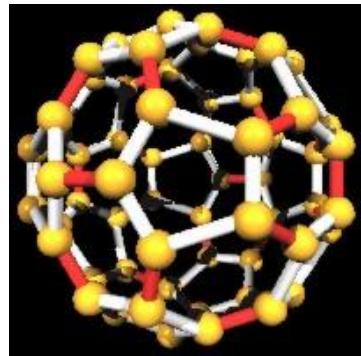


# Computational methods: accuracy versus size



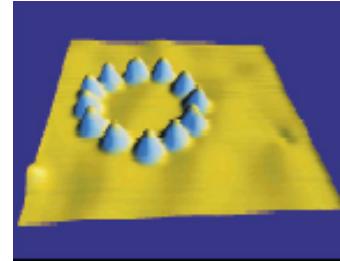
Accuracy

*GW/BSE,  
Coupled Cluster*

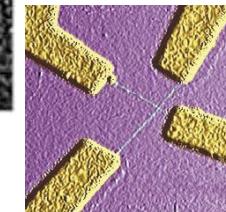
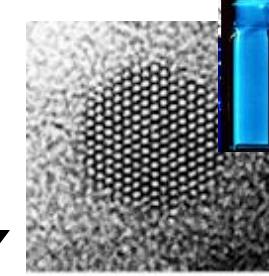


*Time dependent  
DFT*

*Direct LDA*



*Non-selfconsistent  
LDA*



*Empirical  
Pseudopotential*

$10^1$

$10^2$

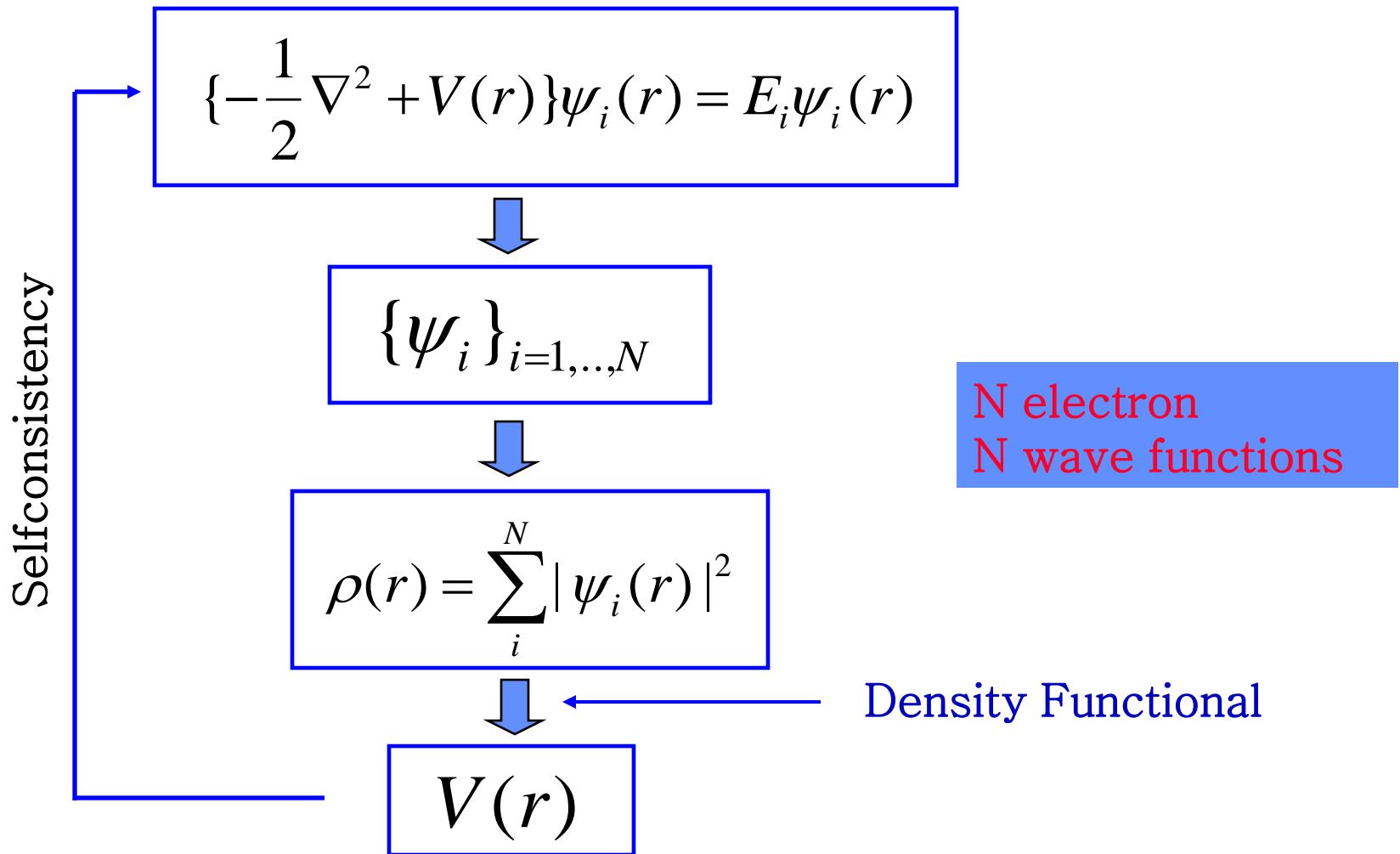
$10^3$

$10^4$   $10^5$

$10^6$

Number of atoms

# Ab initio density functional calculations



## Two tasks for a hybrid nano computation method

(1) To get the potential  $V(r)$  [or the charge density  $\rho(r)$ ]  
so we will have the Hamiltonian.

(We want ab initio reliability, but not a full ab initio calculation)

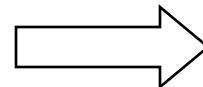
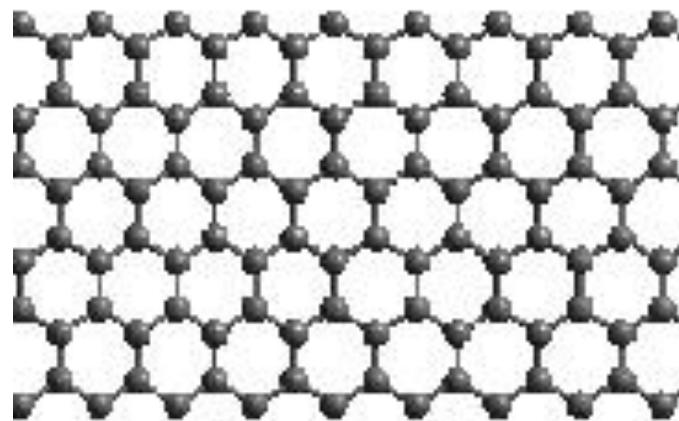
(2) To solve the single particle Hamiltonian  
(Schroedinger's equation), to get the physical properties.

$$\left\{-\frac{1}{2}\nabla^2 + V(r)\right\}\psi_i(r) = E_i\psi_i(r)$$

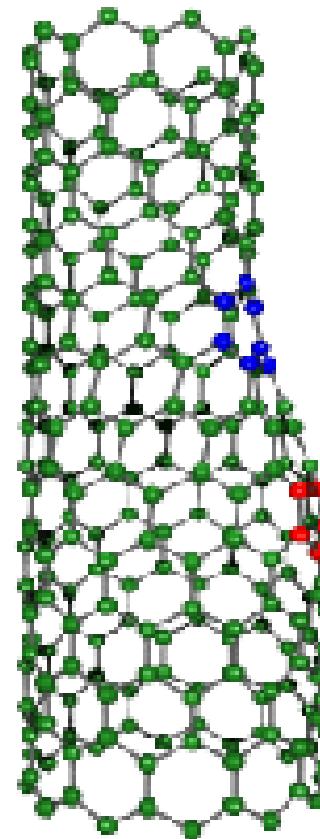
(Not the usual PDE, many eigen states, don't want and need to solve all of them)

## Charge patching method

Selfconsistent LDA  
calculation of a single  
graphite sheet



Non-selfconsistent LDA  
quality potential for  
nanotube



Get information from small  
system ab initio calc., then generate  
the charge densities for large systems

# Charge patching: free standing quantum dots

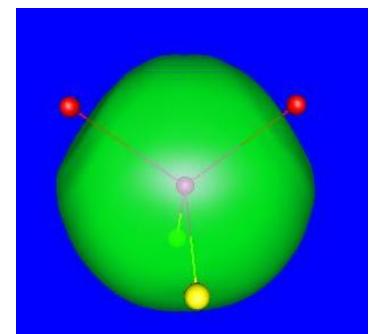
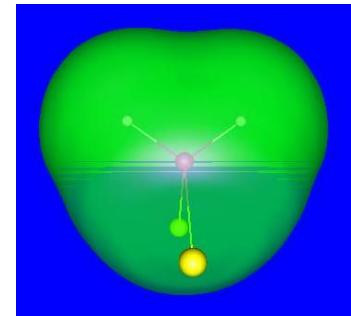
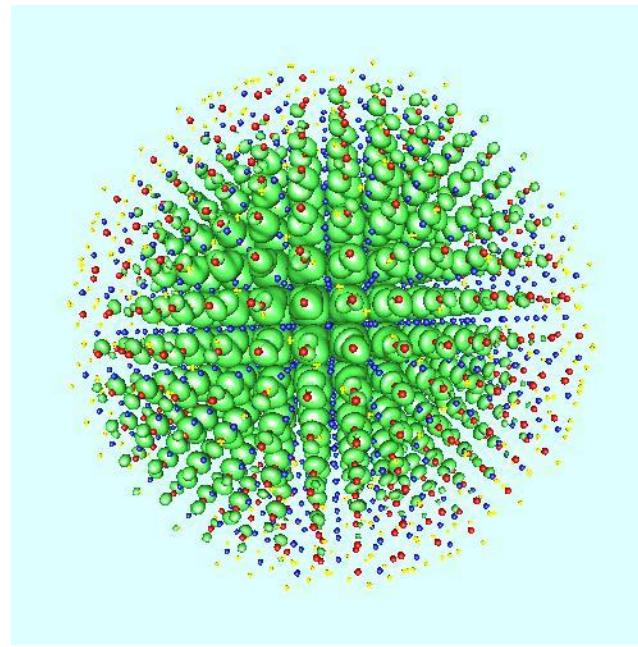
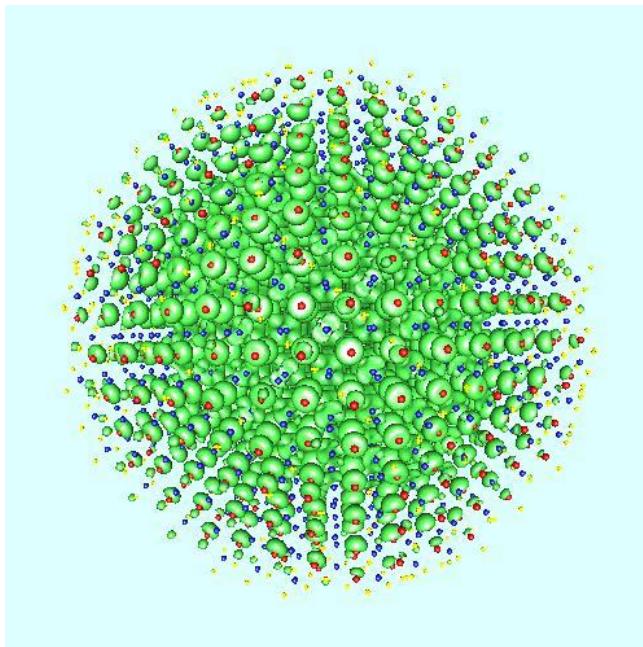
$\text{In}_{675}\text{P}_{652}$  LDA quality calculations (eigen energy error  $\sim 20$  meV)

64 processors (IBM SP3) for  $\sim 1$  hour

CBM

VBM

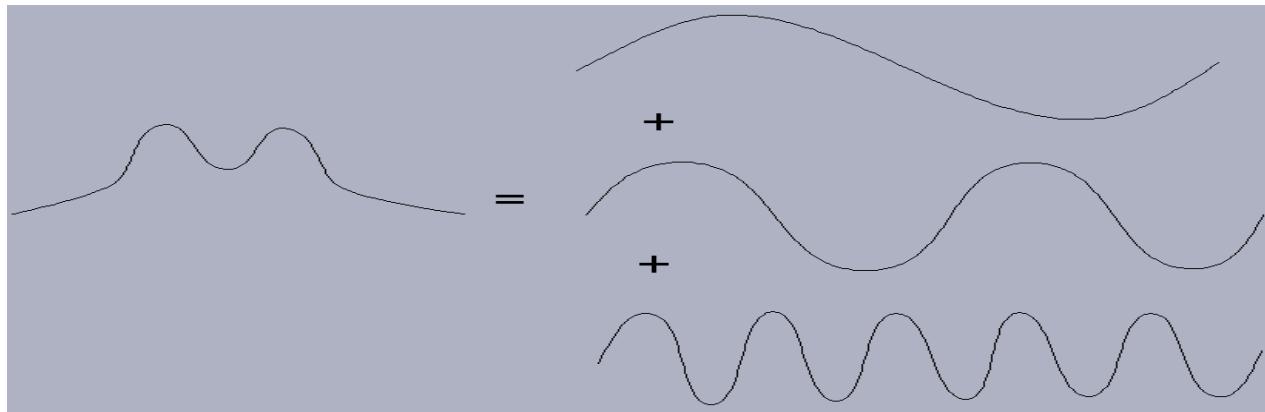
Total charge density  
motifs



# Planewave expansion of the wavefunction

$$\left\{ -\frac{1}{2} \nabla^2 + V(r) \right\} \psi_i(r) = E_i \psi_i(r)$$

$$\psi(r) = \sum_q C(q) e^{iqr}$$



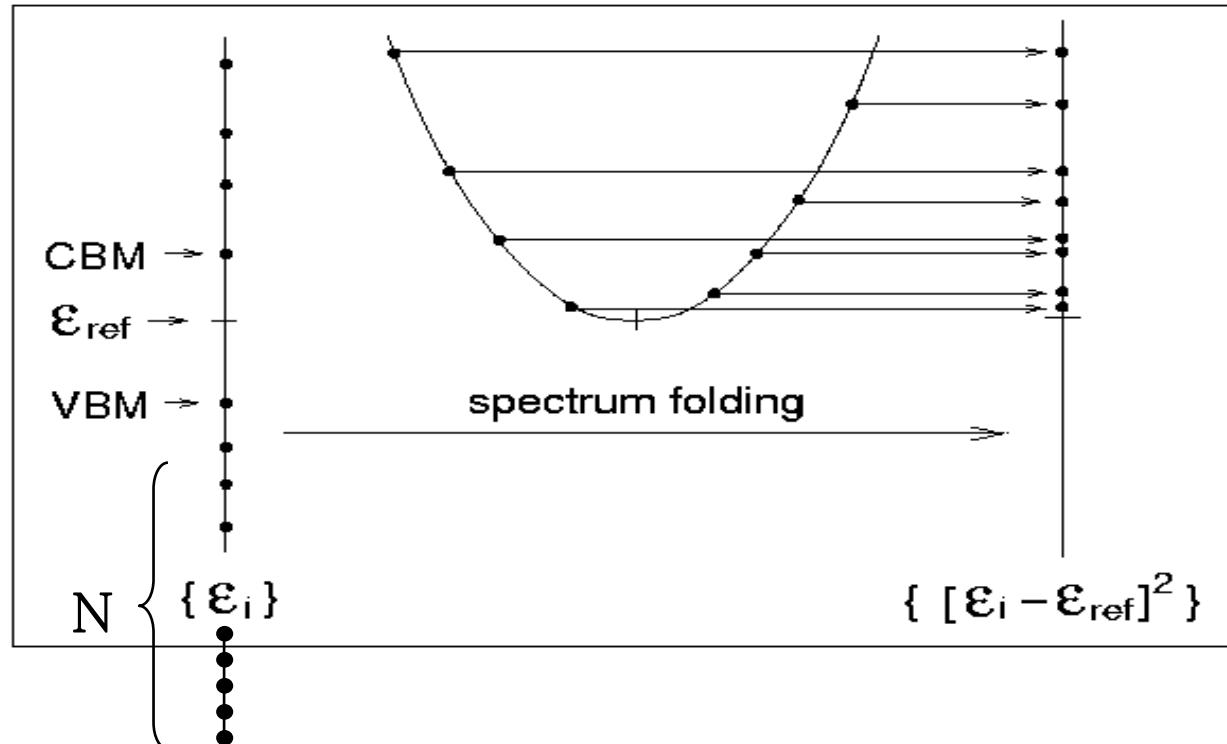
Fast Fourier Transformation between  
real space  $\psi(r)$  and Fourier space  $C(q)$ .

# Folded Spectrum Method

$$\left\{ -\frac{1}{2} \nabla^2 + V(r) \right\} \psi_i(r) = E_i \psi_i(r)$$

$$H\psi_i = \varepsilon_i \psi_i$$

$$(H - \varepsilon_{ref})^2 \psi_i = (\varepsilon_i - \varepsilon_{ref})^2 \psi_i$$



## NERSC: National Energy Research Scientific Computing Center



Hopper, Cray XE6 machine, 150,000 computing cores, 1.3 Petaflops

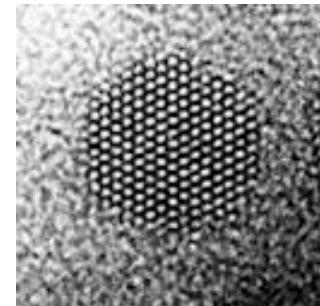
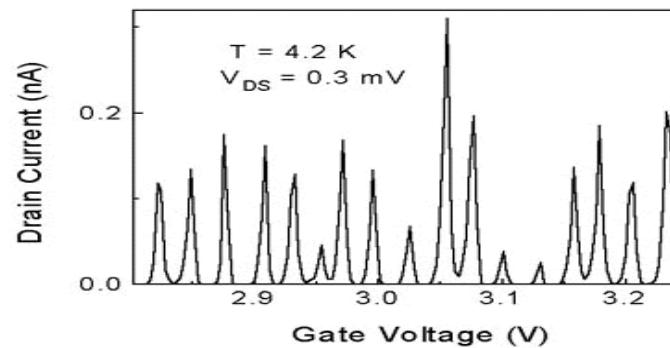
## Examples of new properties

- Band gap increase

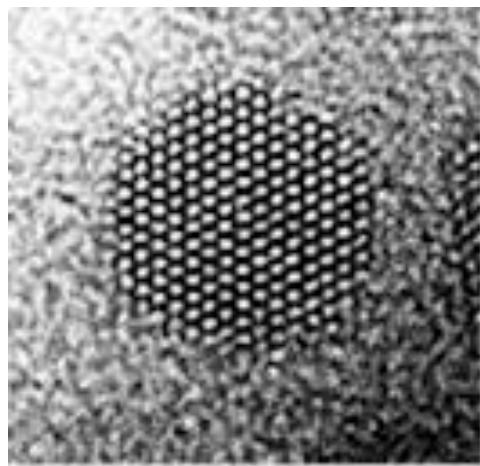


CdSe quantum dot

- Single electron effects on transport (Coulomb blockade).
- Mechanical properties, surface effects and no dislocations



# Free standing quantum dots



CdSe  
quantum dot  
TEM image

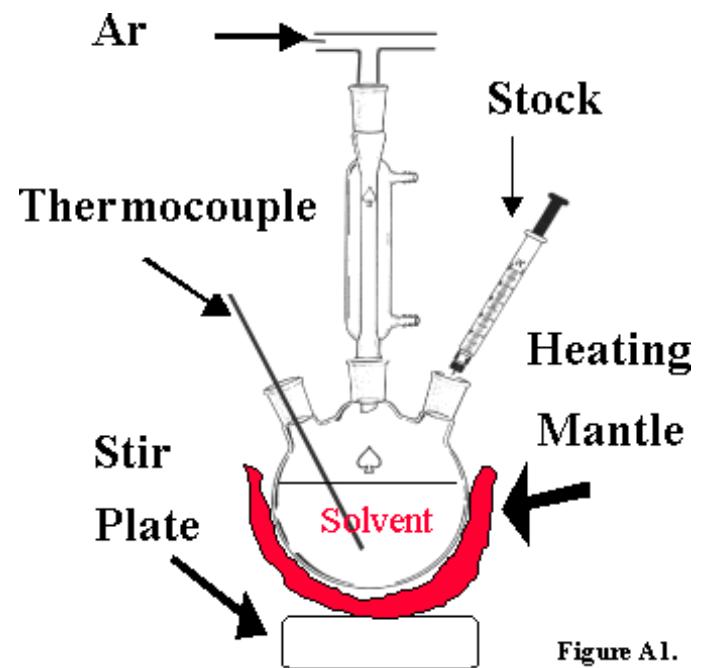
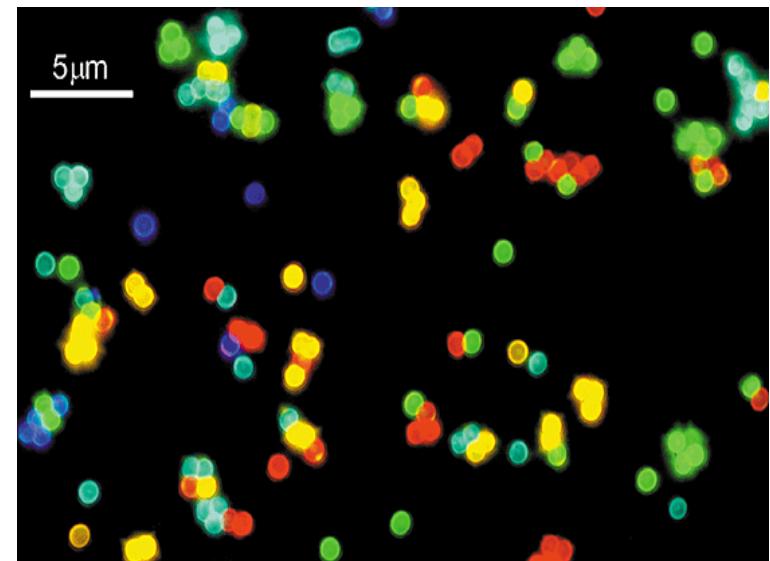
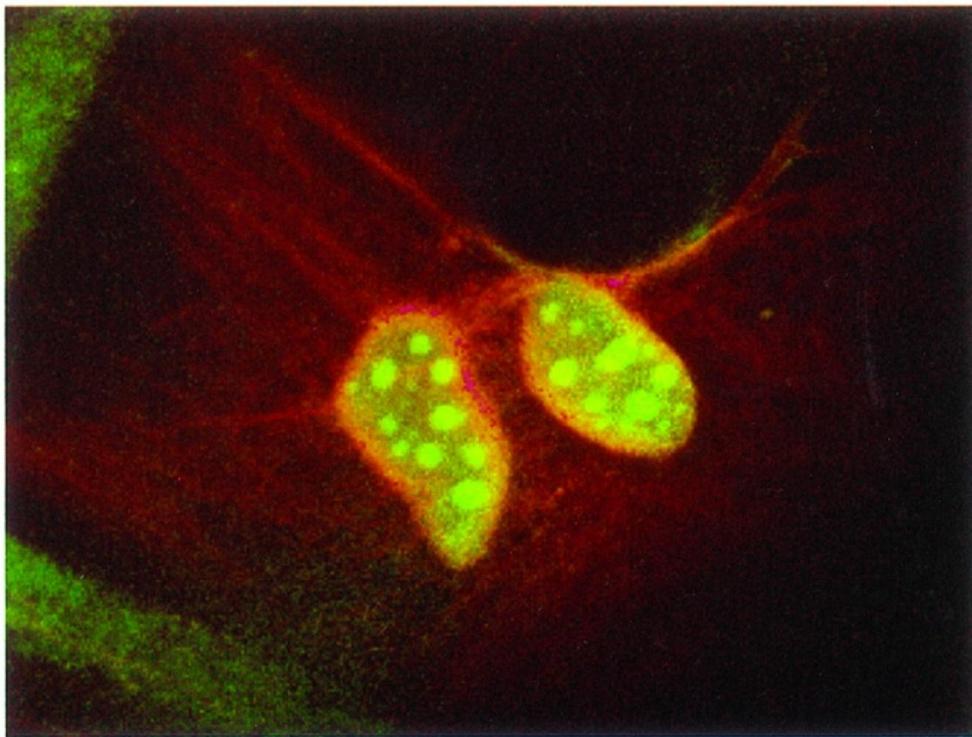


Figure A1.

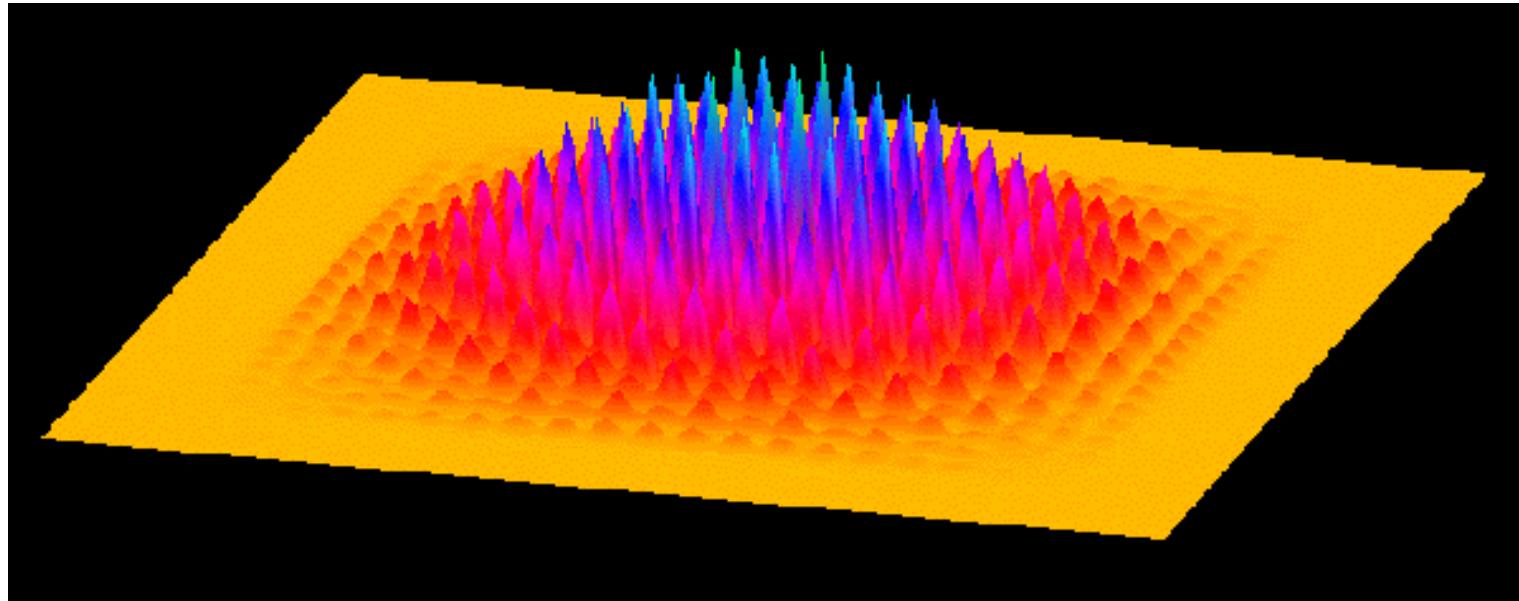
- Chemically synthesised
- Interior atoms are in bulk crystal structure
- Surface atoms are passivated
- Diameter  $\sim 20\text{--}100\text{ \AA}$
- A few thousand atoms, beyond ab initio method

# CdSe quantum dots as biological tags



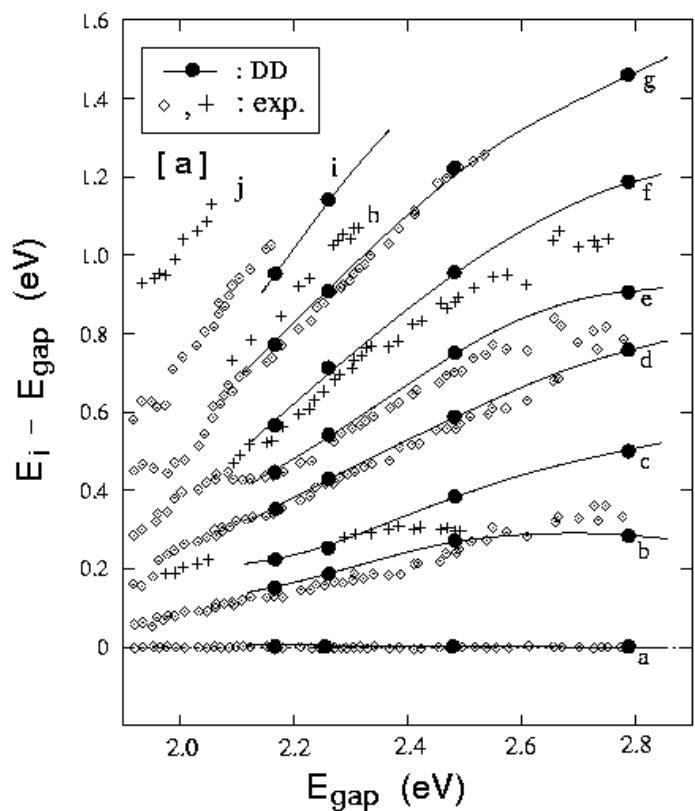
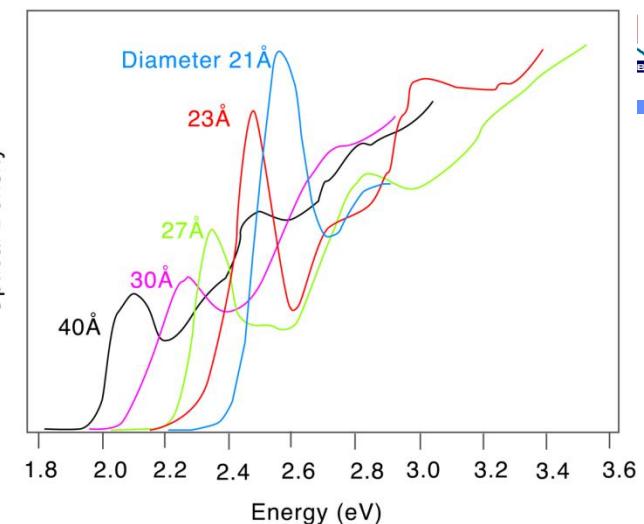
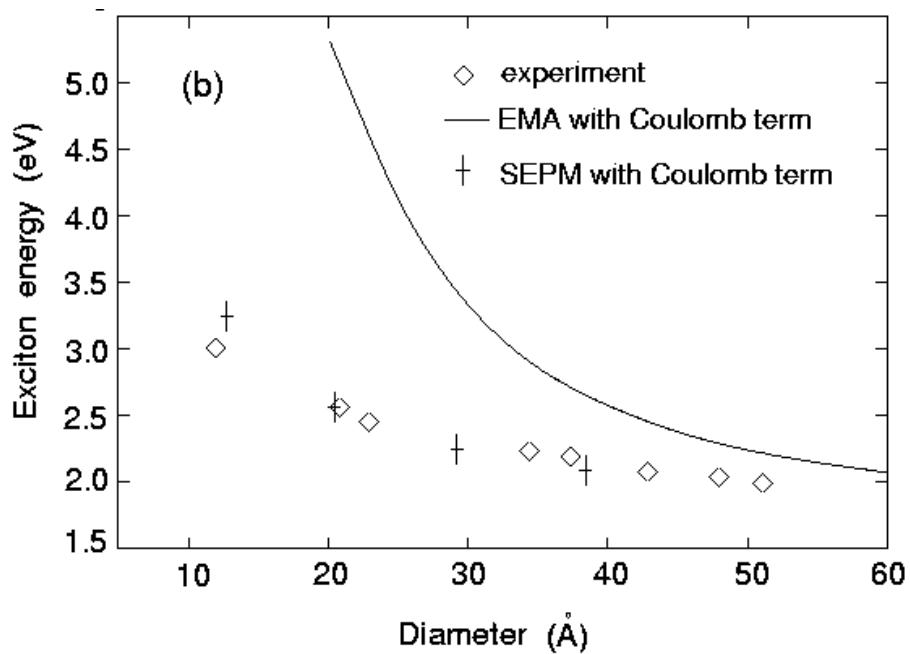
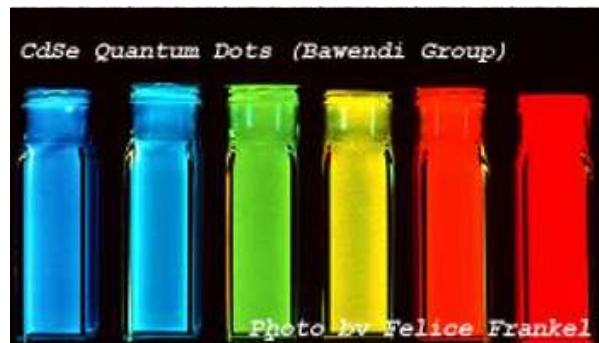
- Optically more stable than dye molecules
- Can have multiple colors

# Quantum dot wavefunctions

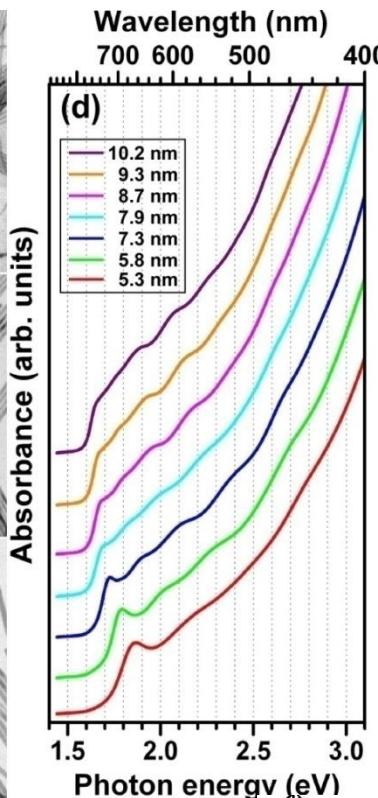
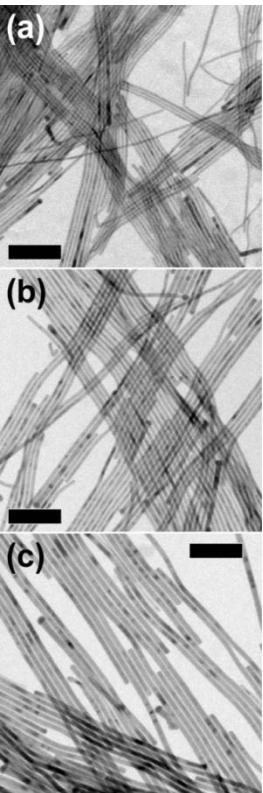


Cross section electron wavefunctions

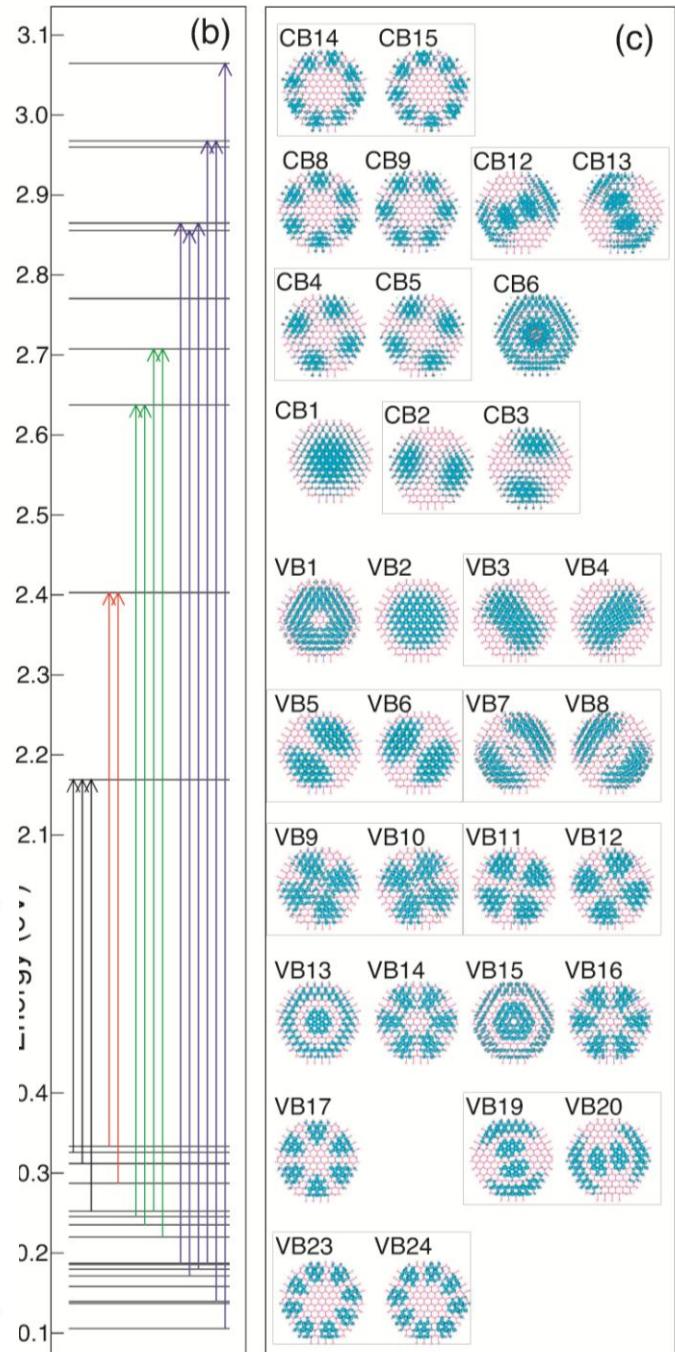
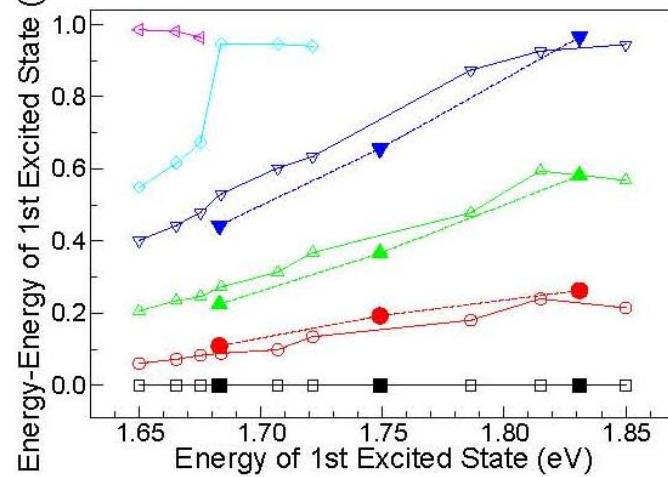
# CdSe quantum dot results



# CdTe nanowire



Exp: —  
Calc: - - -



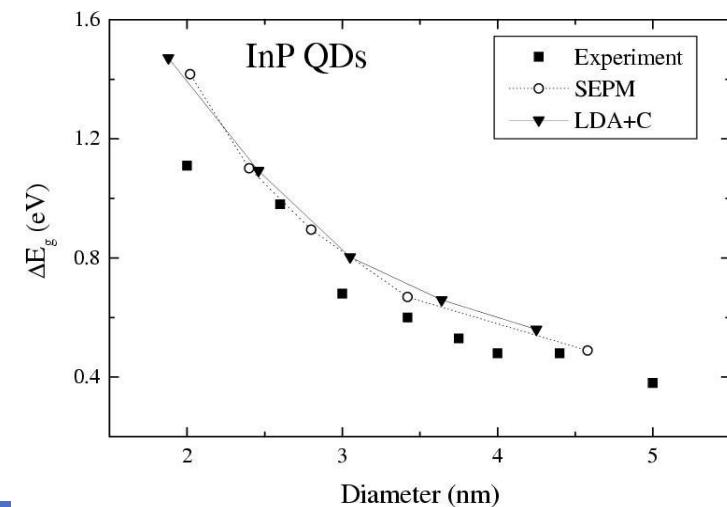
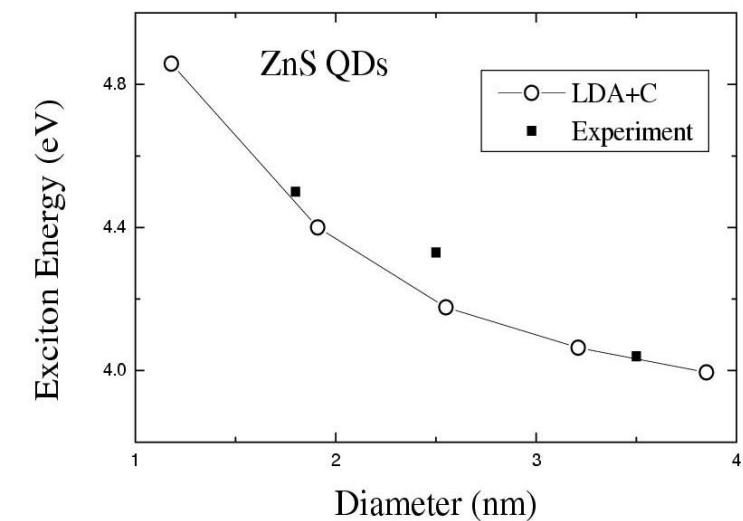
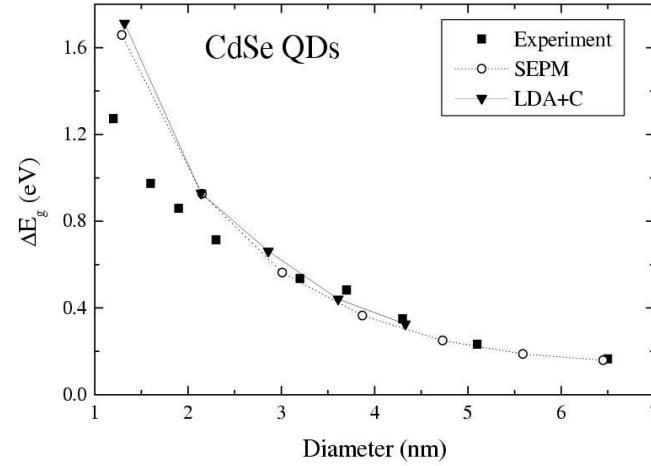
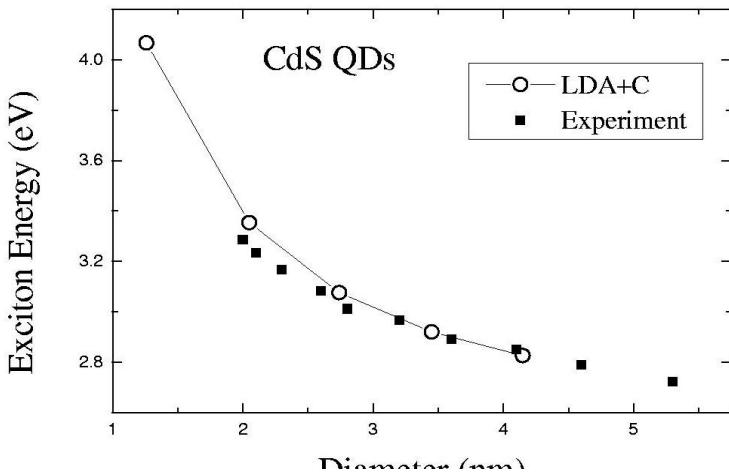
# Quantum dot and wire calculations for semiconductor materials



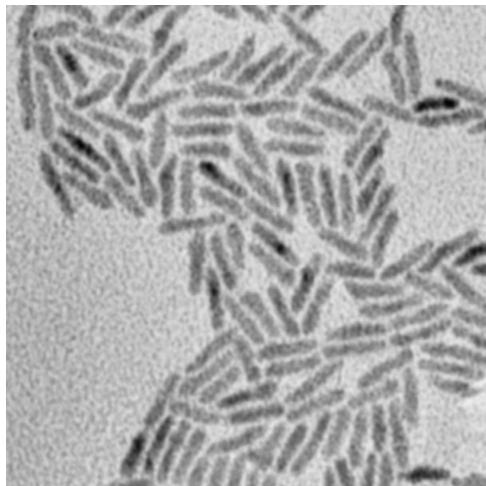
IV-IV: Si

III-V: GaAs, InAs, InP, GaN, AlN, InN

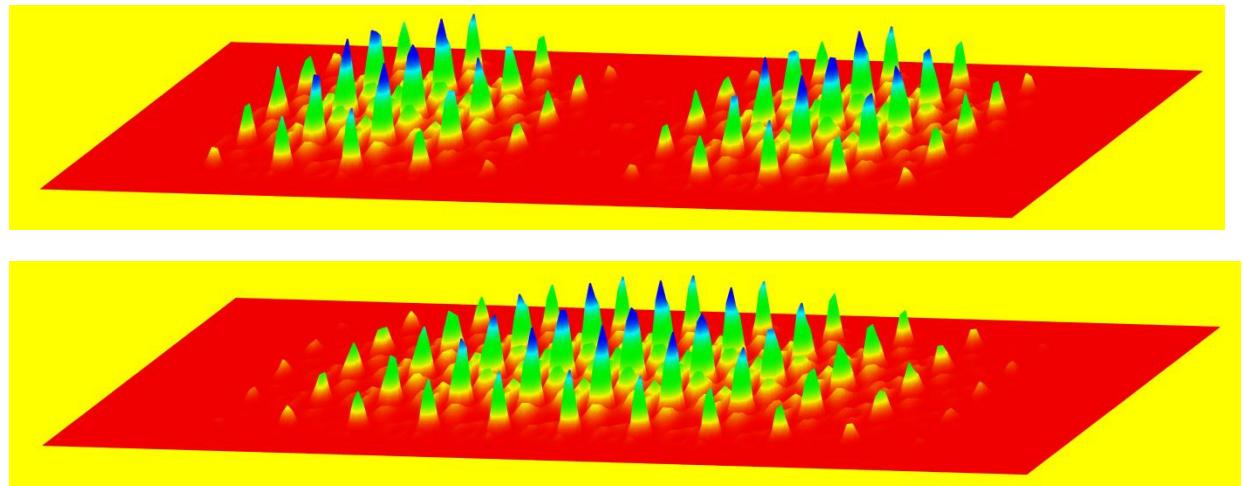
II-VI: CdSe, CdS, CdTe, ZnSe, ZnS, ZnTe, ZnO



# Polarization of CdSe quantum rods

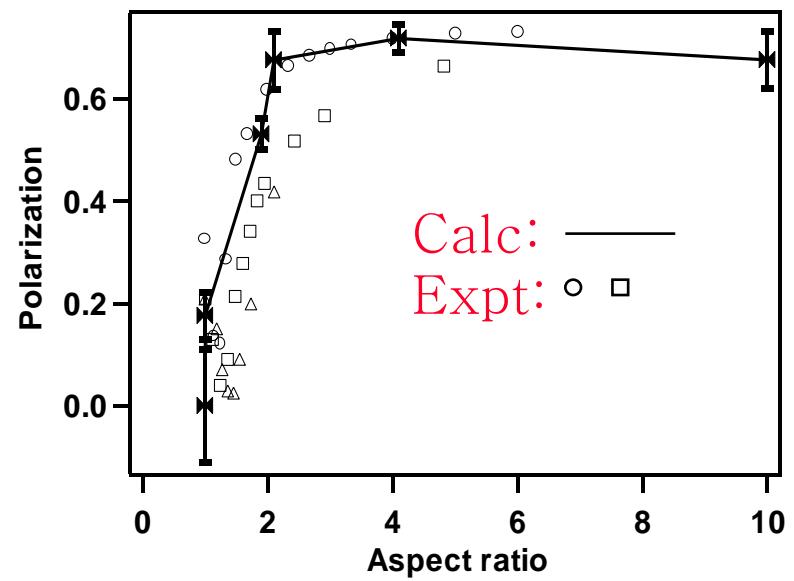
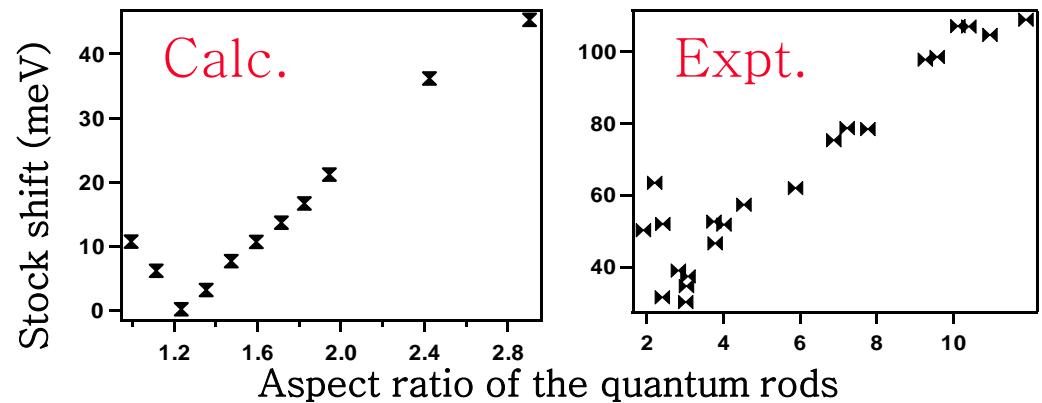
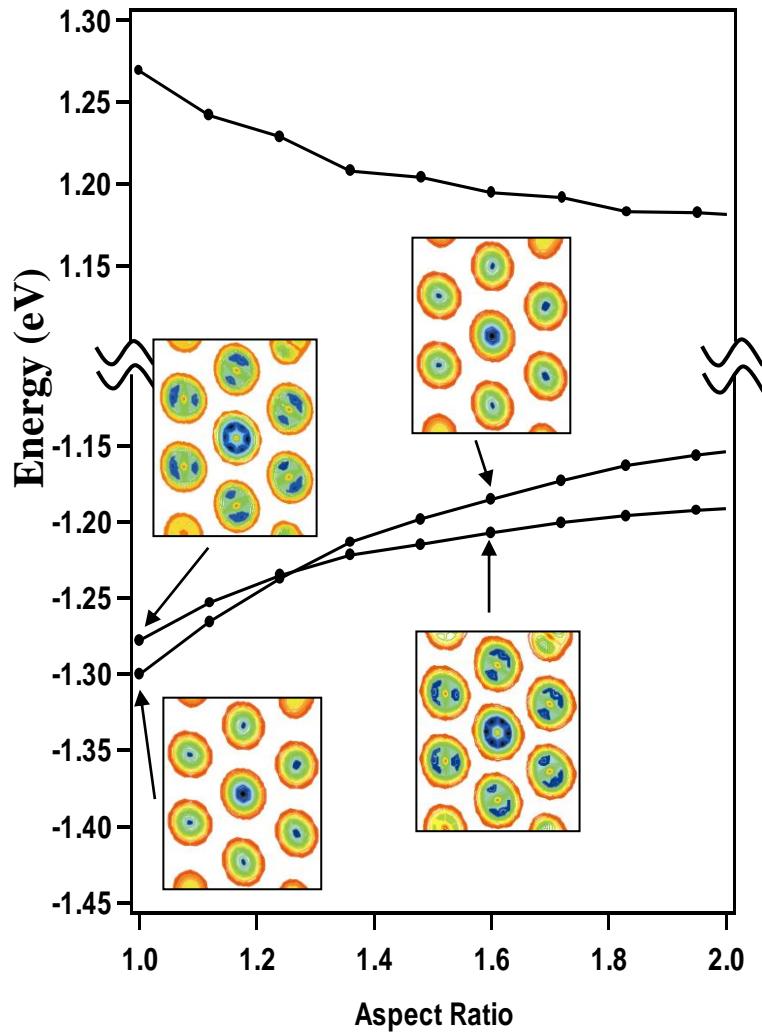


CdSe quantum rods

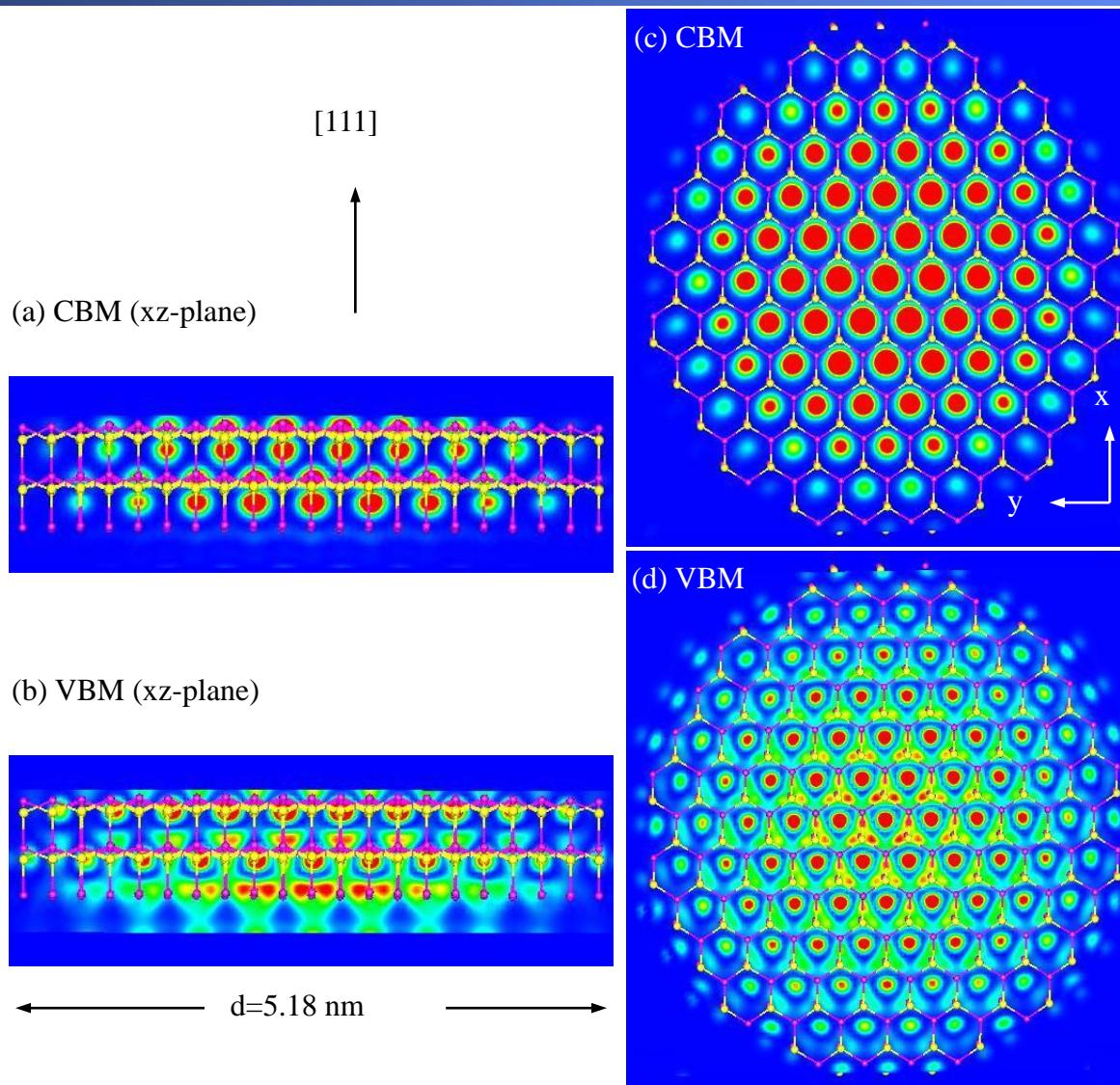


The electron wavefunctions of a quantum rods

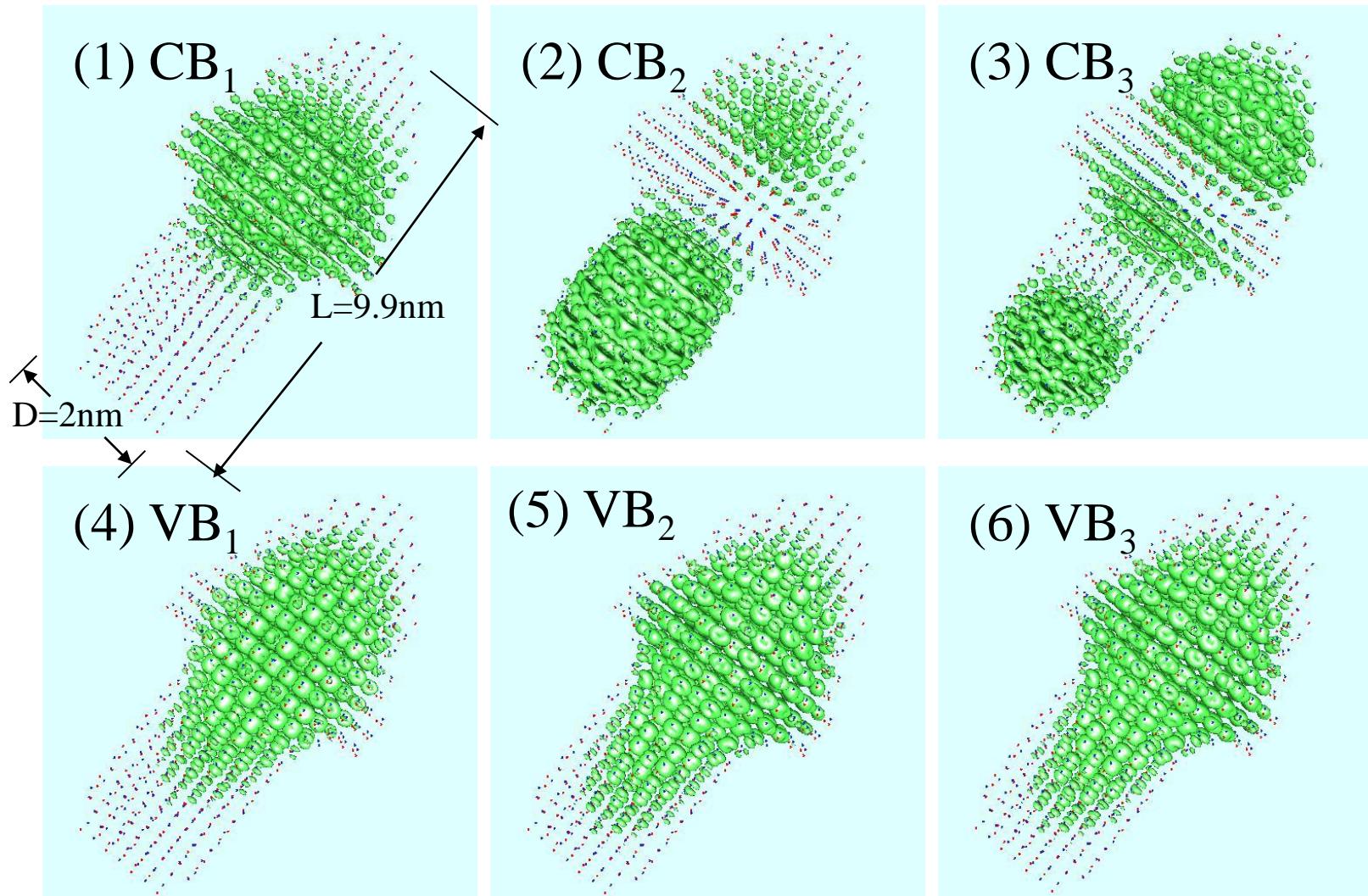
# Polarization of quantum rods (continued)



# Quantum wire electronic states

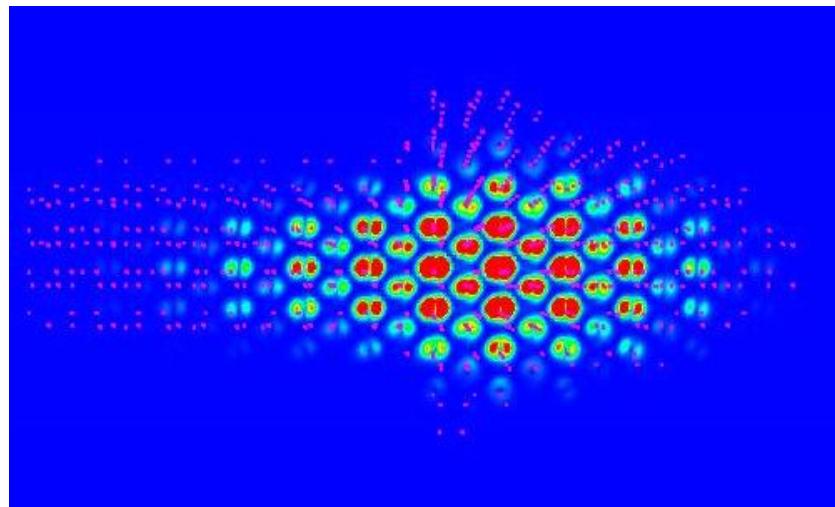


# CdSe quantum dot: arrow shape

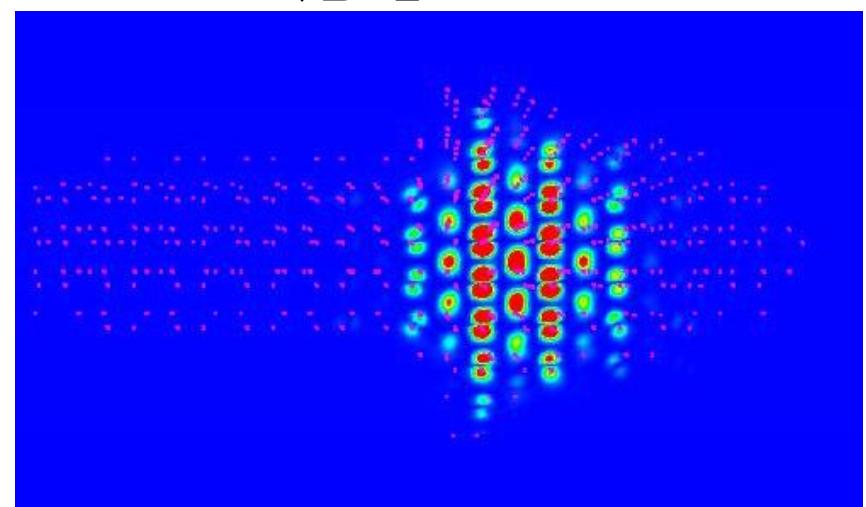


# Different Bloch state characters for the VB states

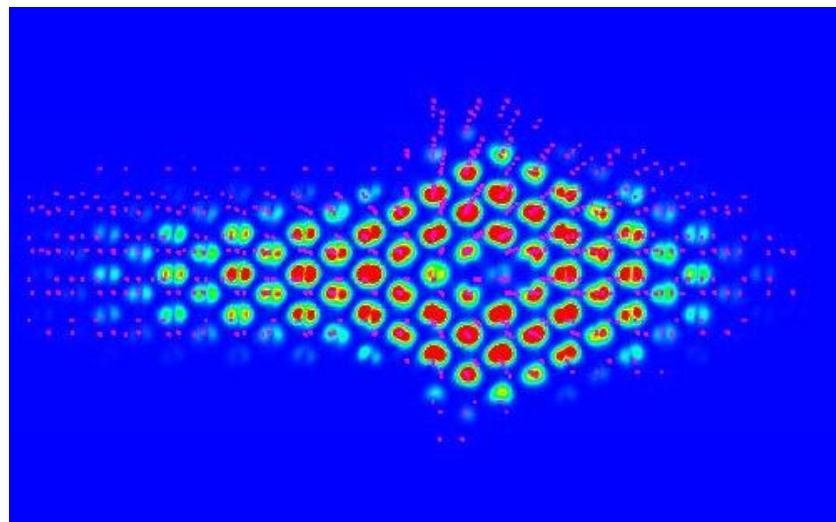
VB-1



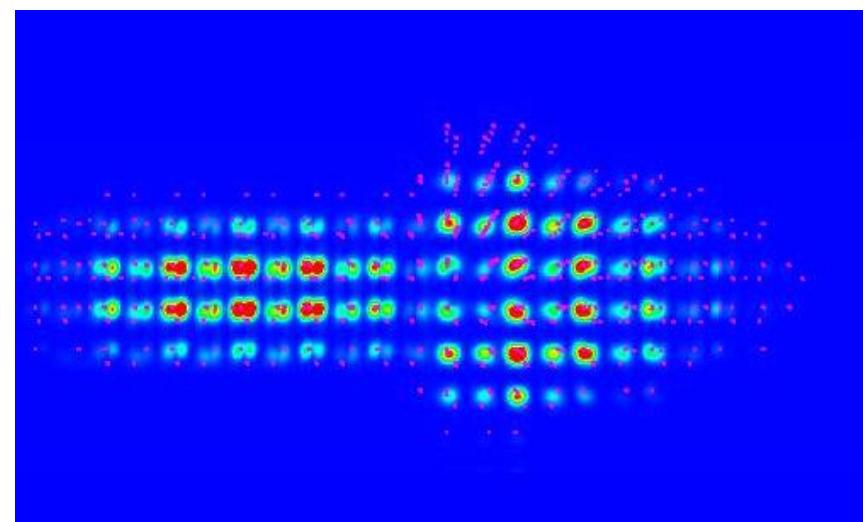
VB-2



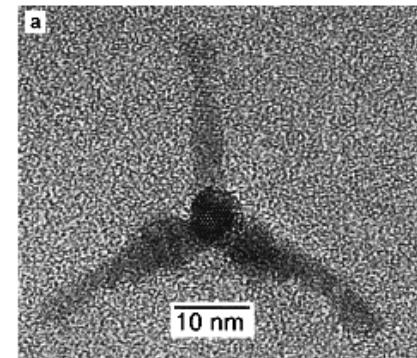
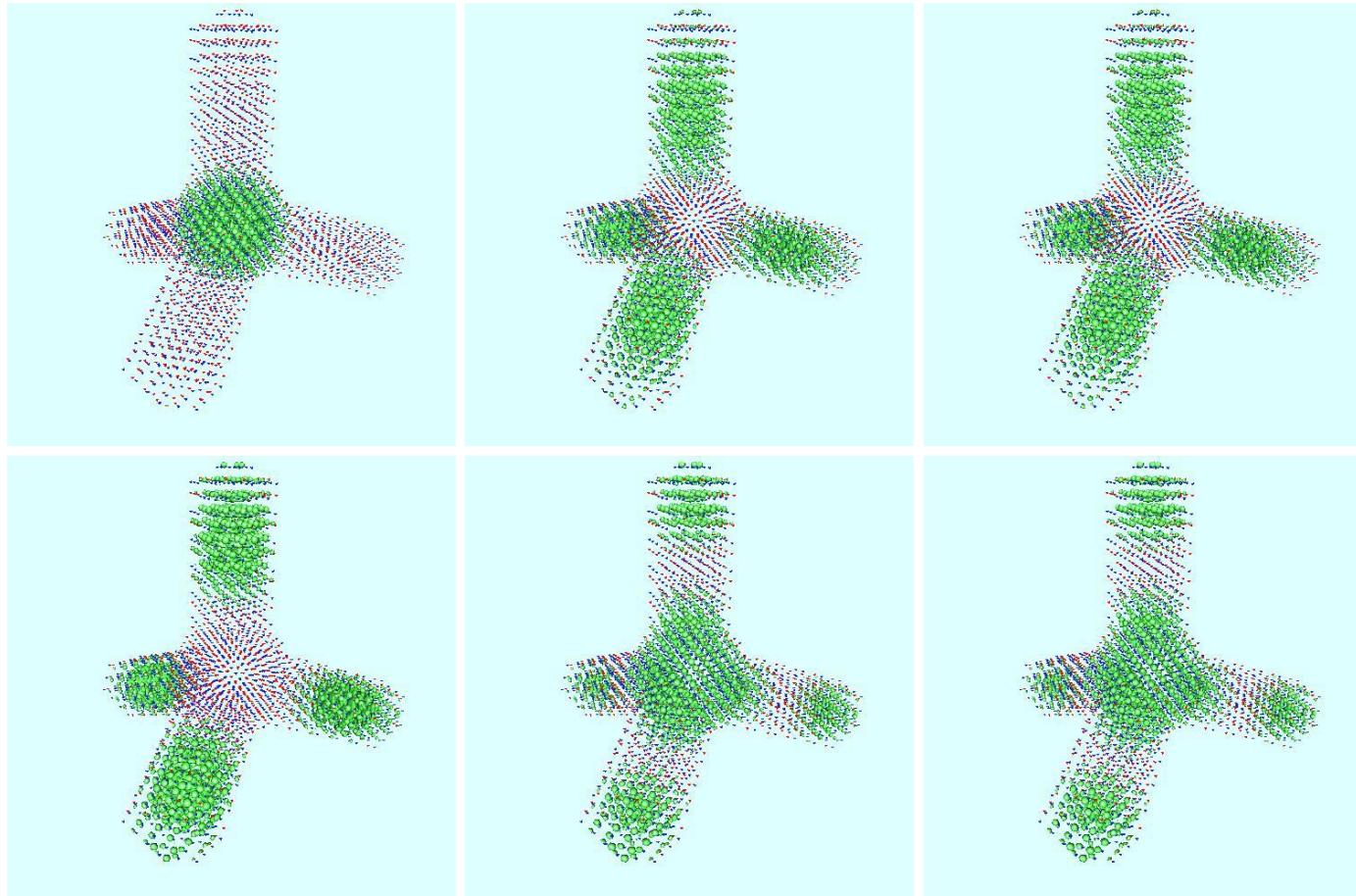
VB-3



VB-4



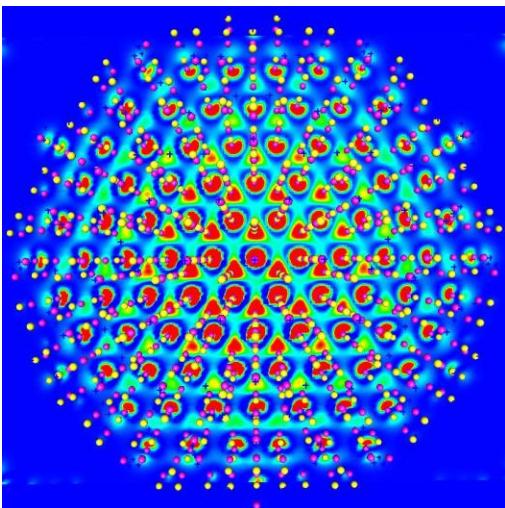
# CdSe tetrapod electronic states



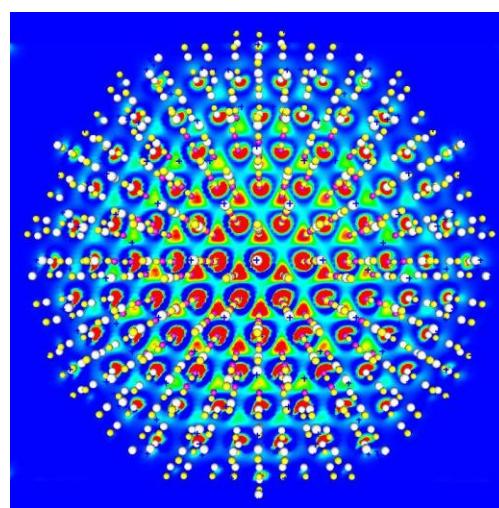
## Core/shell quantum dots

CBM

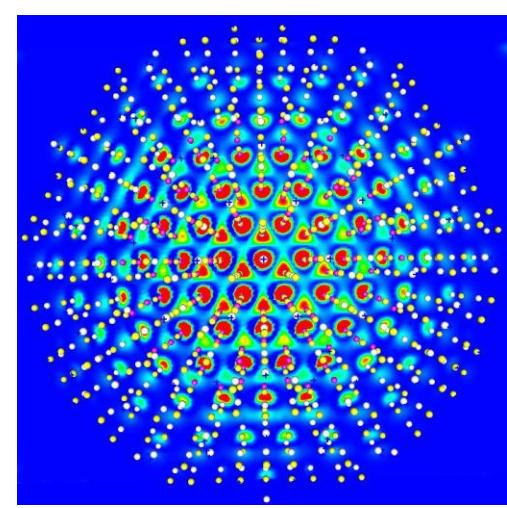
CdSe



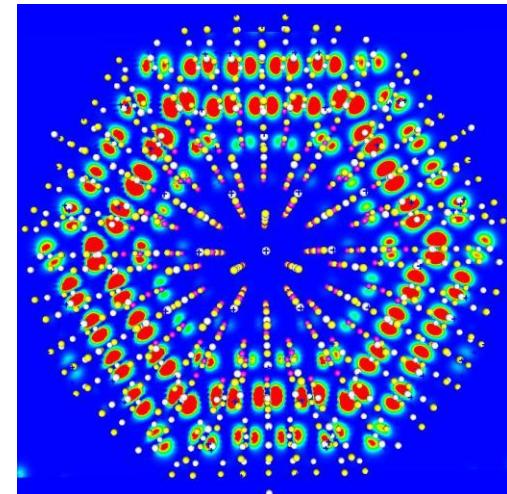
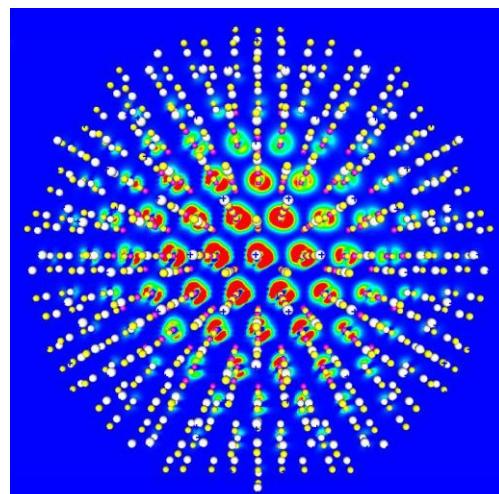
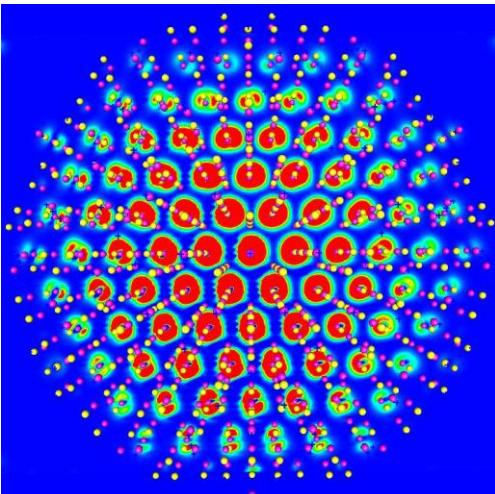
CdSe/CdS



CdSe/CdTe



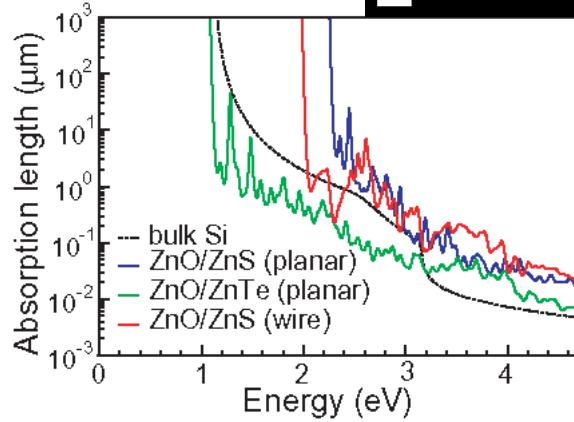
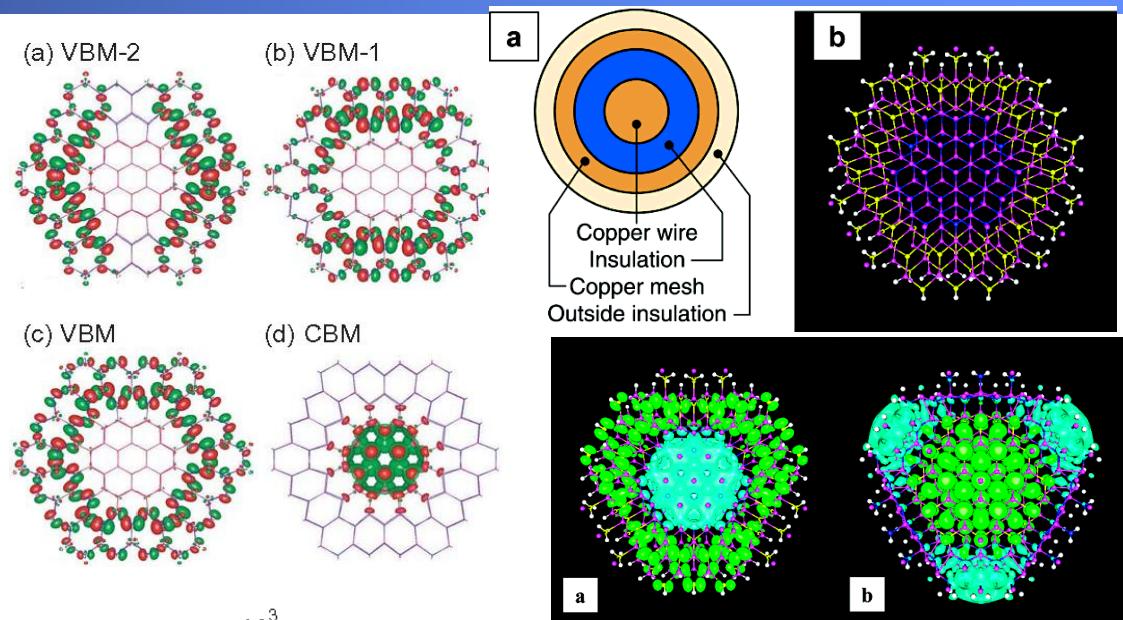
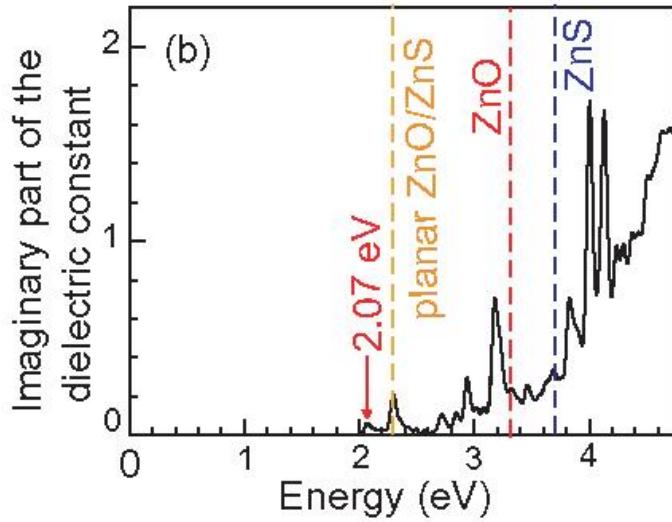
VBM



# Solar cell using stable, abundant, and env. benign mat



## ZnO/ZnS core/shell wire



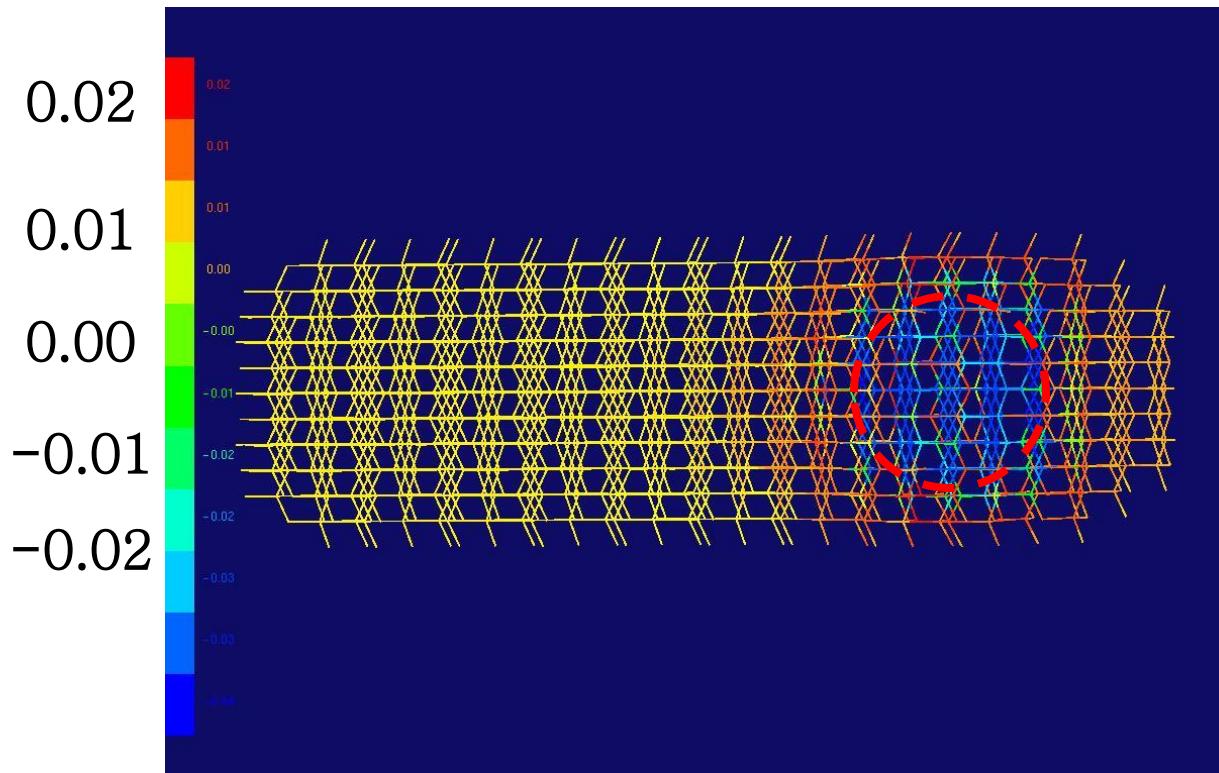
Band gap lowers down further from superlattices.

The absorption length is similar to bulk Si, thus similar among f material for solar cell.

23% theoretical efficiency for solar cell

# CdSe core inside CdS nanorode

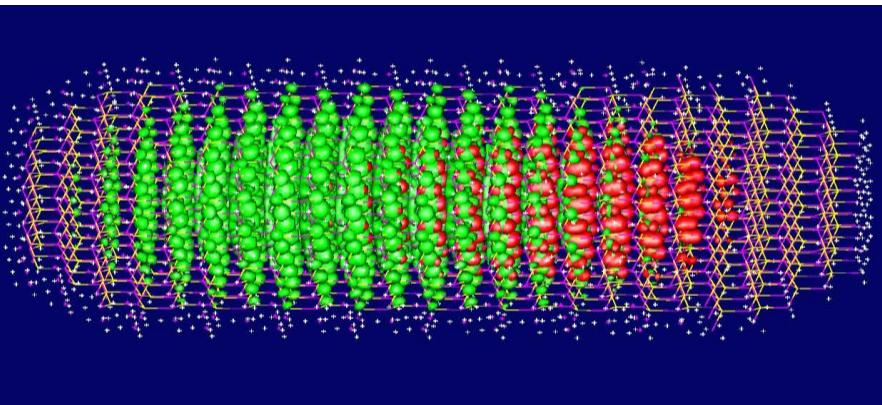
Hydrodynamic strain profile (relaxed using VFF)



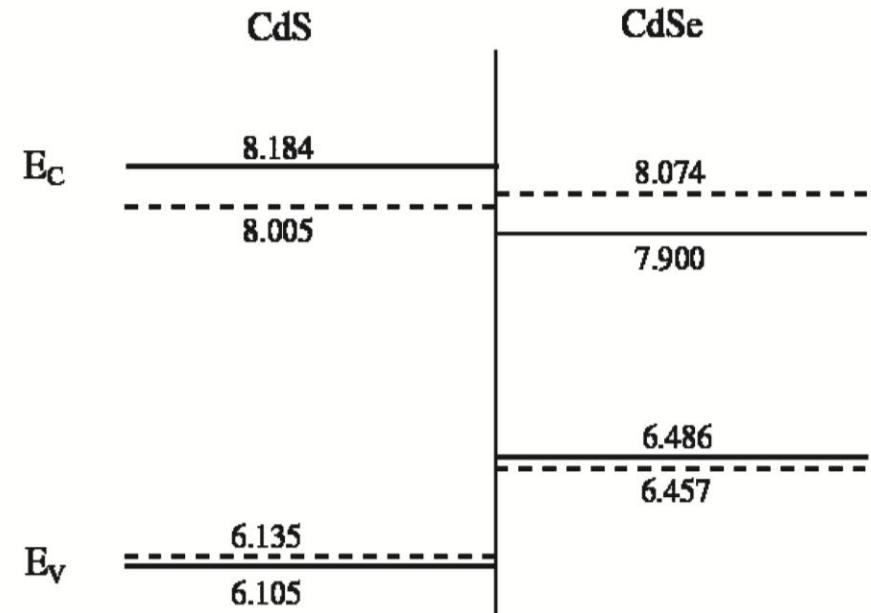
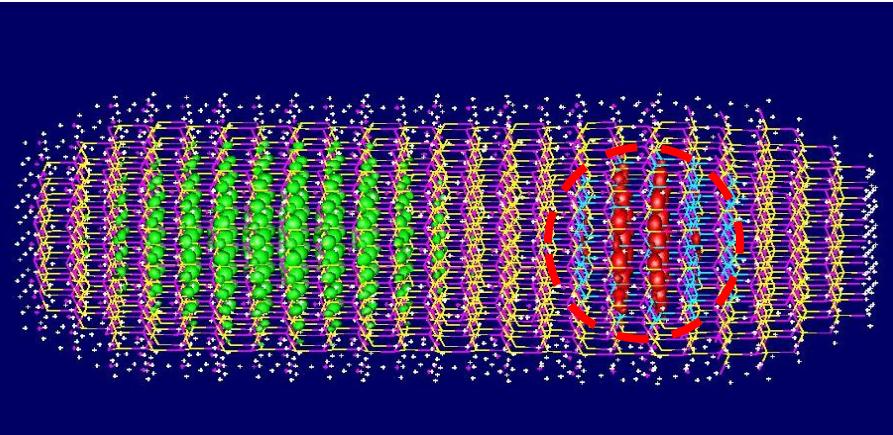
# The effect of the CdSe core to electron and hole



Without core

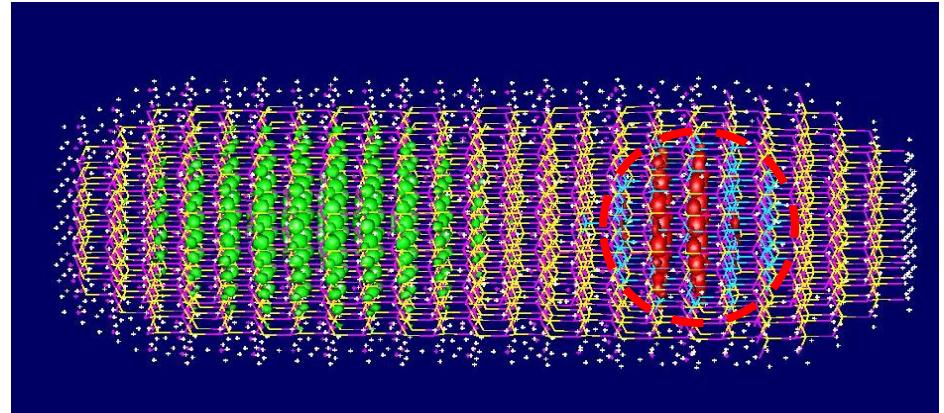
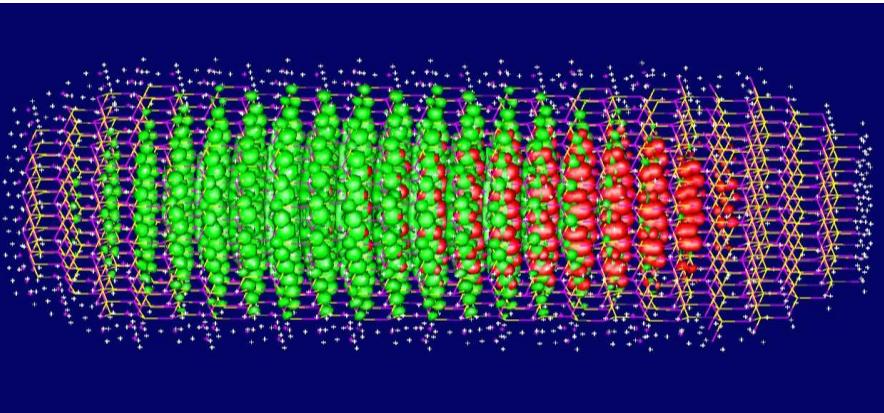


With core

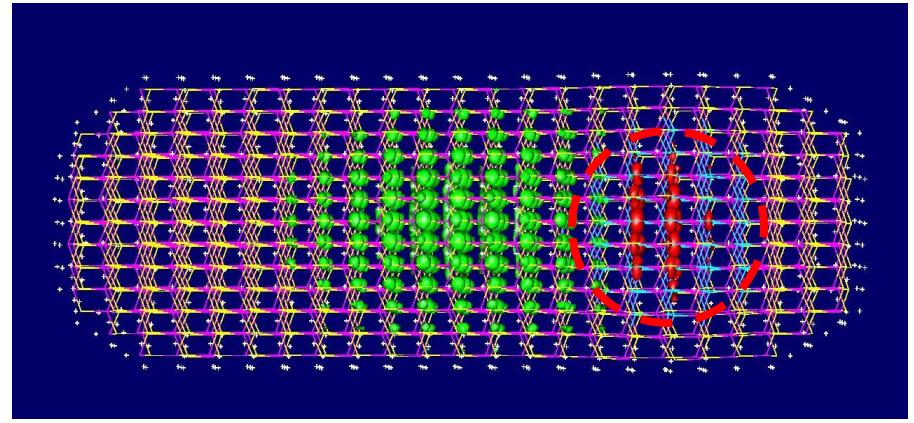
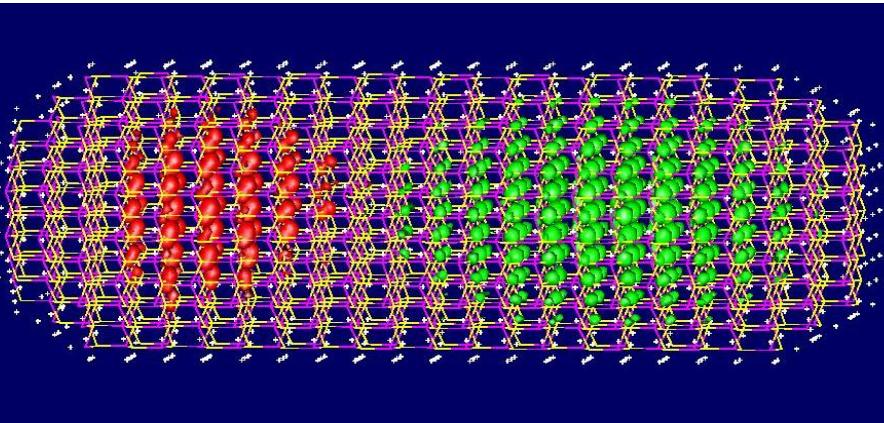


# Effect of surface dipole moment

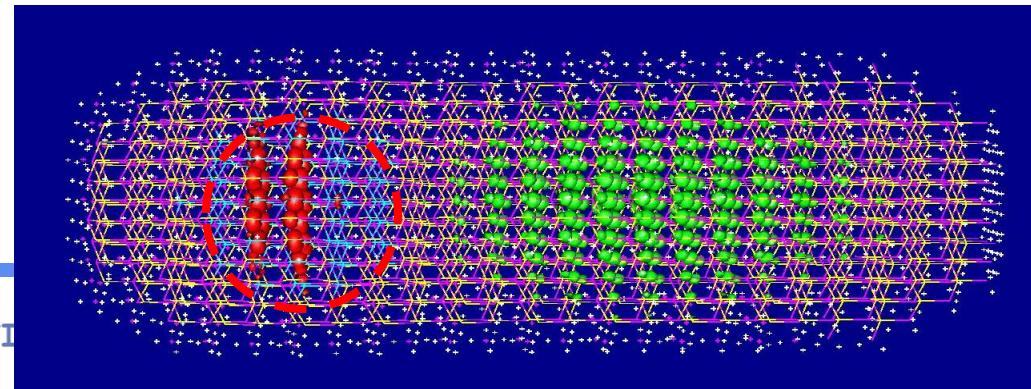
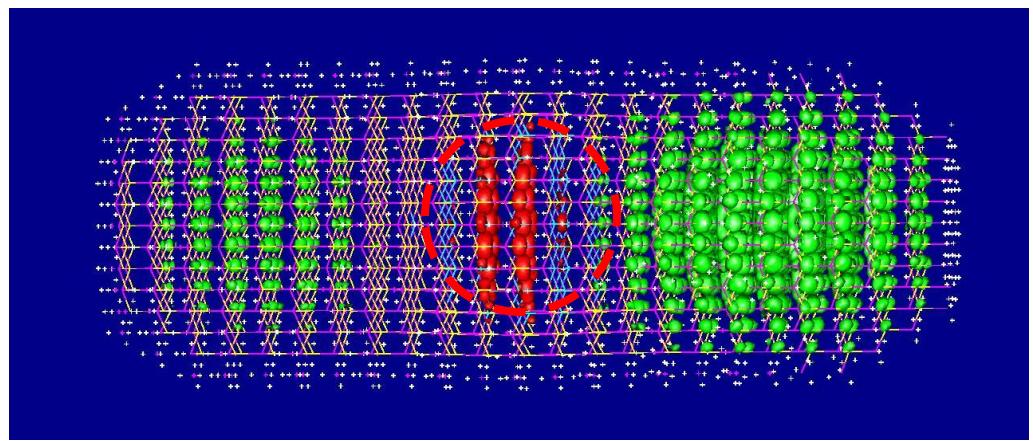
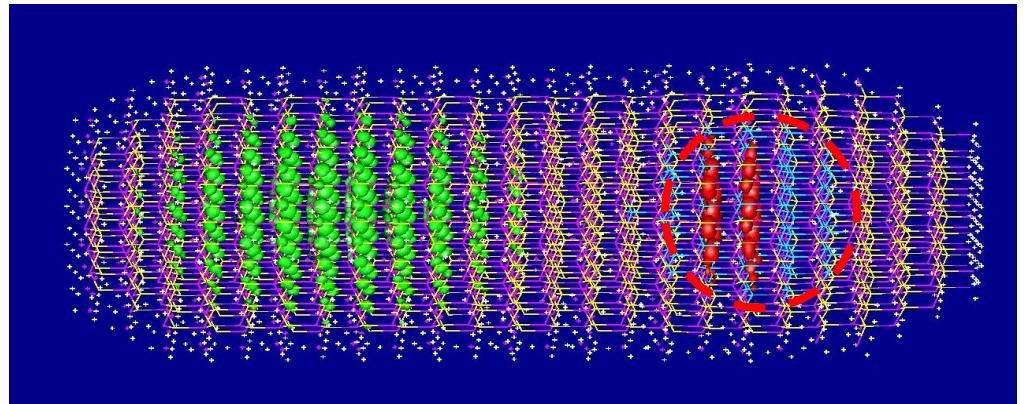
Cd terminated surface



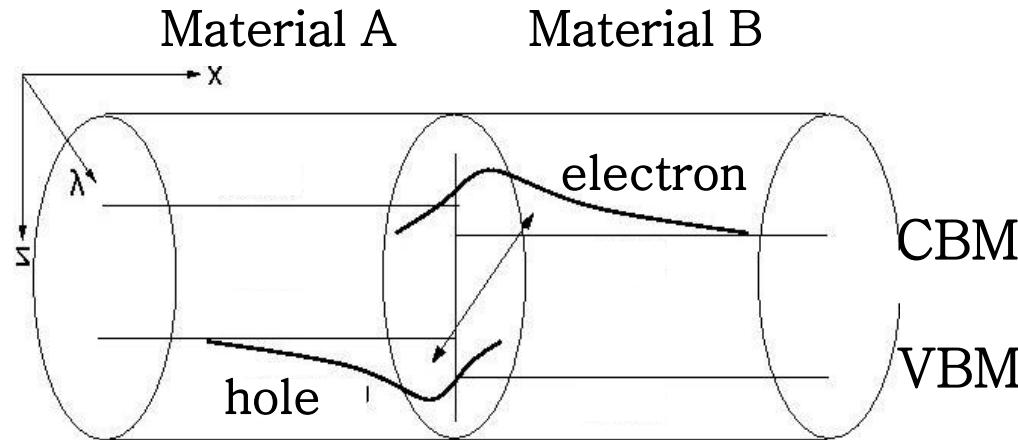
Cd and Se terminated surface



# The shift of CdSe core



# How to calculate an exciton in nanosystem?



What is the binding energy of the interface exciton ?

The approach: GW+ BSE

Approximation: GW  $\rightarrow$  LDA+ C (for bulk short range effect)  
 $P(r)$  (surface image potential, for long range effect)

BSE  $\rightarrow$  CI calculation

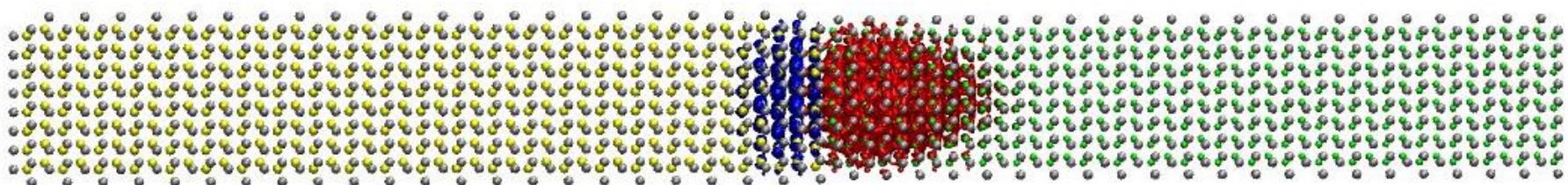
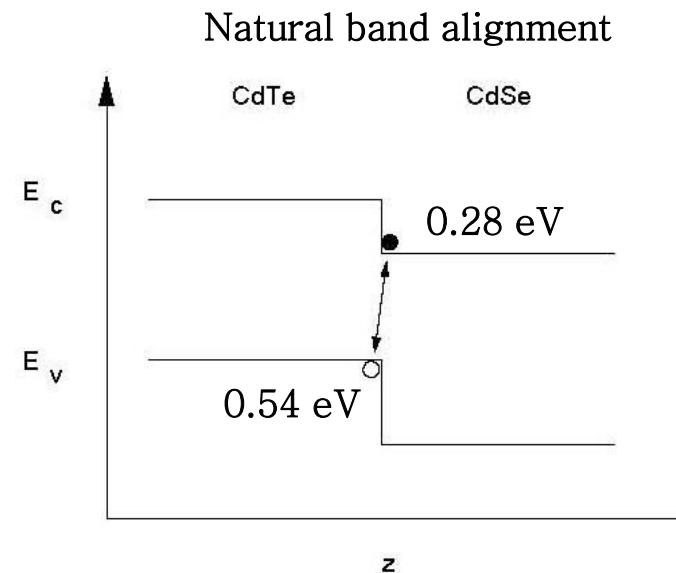
# A selfconsistent calculation for a bound exciton

$$\left\{ -\frac{1}{2} \nabla^2 + V_{LDA+C}(r) + P(r) - V_v(r) \right\} \psi_c(r) = \varepsilon_c \psi$$

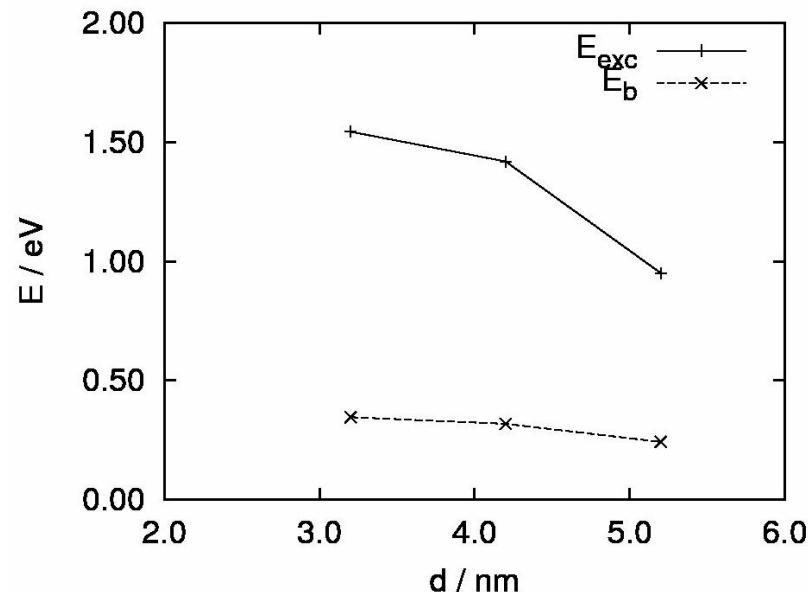
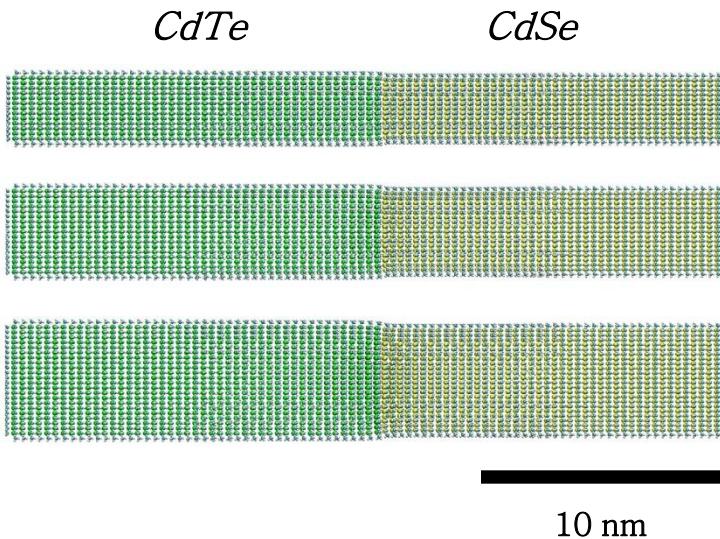
$$\left\{ -\frac{1}{2} \nabla^2 + V_{LDA+C}(r) - P(r) + V_c(r) \right\} \psi_v(r) = \varepsilon_v \psi$$

$$\nabla[\varepsilon(r)\nabla V_{C(V)}(r)] = 4\pi\psi_{V(C)}^2(r)$$

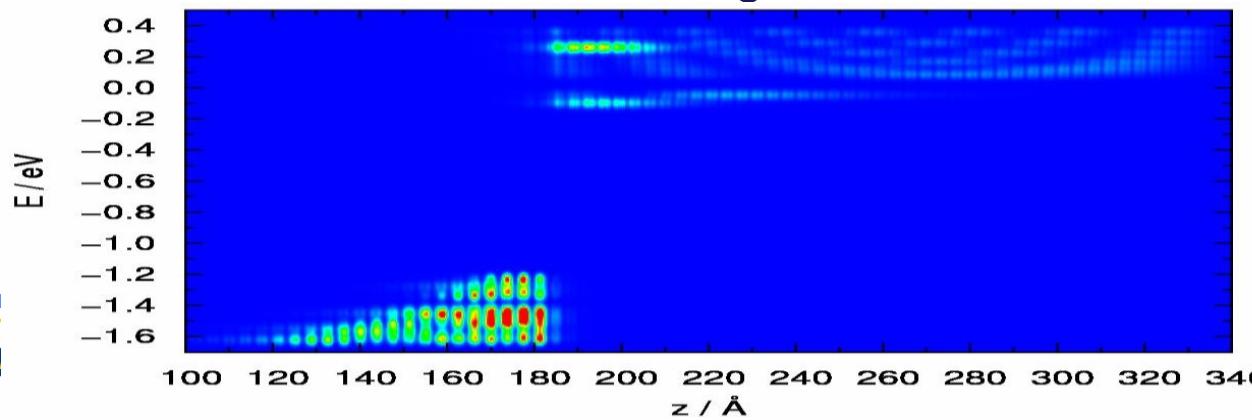
$$P(r) = \frac{1}{2} \lim_{r' \rightarrow r} [W(r, r') - W_{bulk}(r, r')]$$



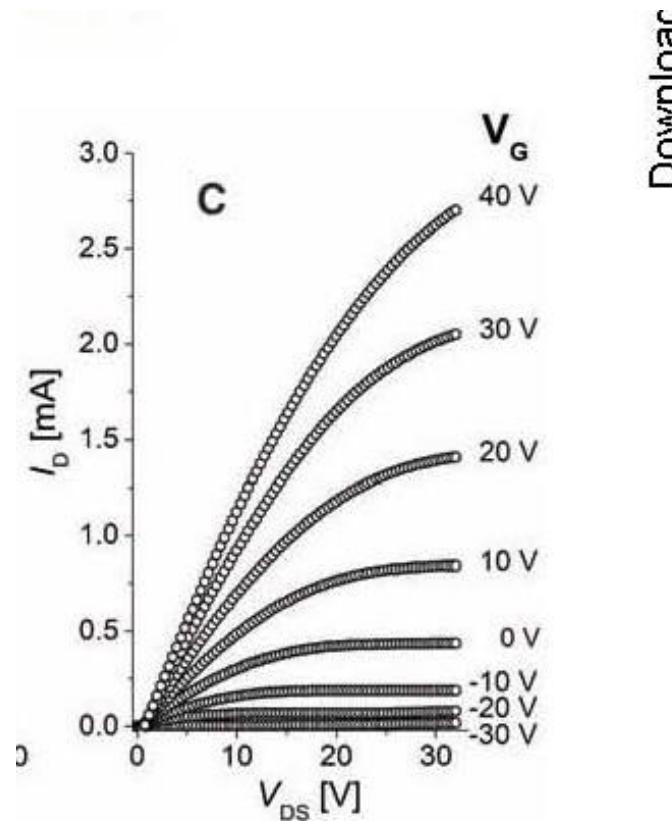
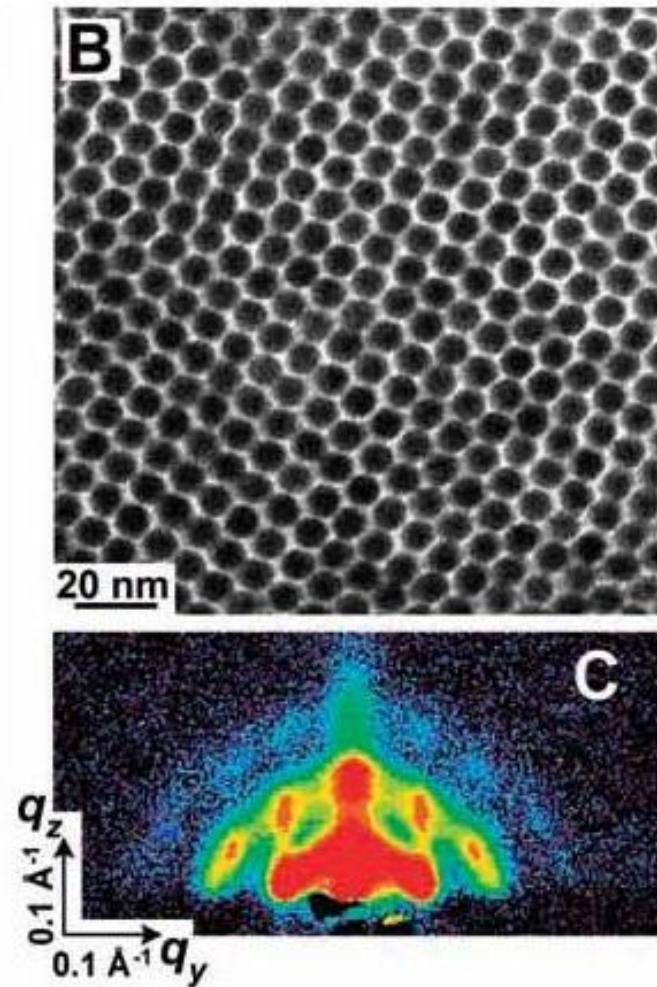
# CdSe/CdTe Nanorods



- ◆ Exciton binding energy: 0.4 to 0.25 eV
- ◆ Exciton radiative recombination life time:  $\sim 1 \mu\text{s}$
- ◆ Correlation effect: < 1 meV for ground exciton state



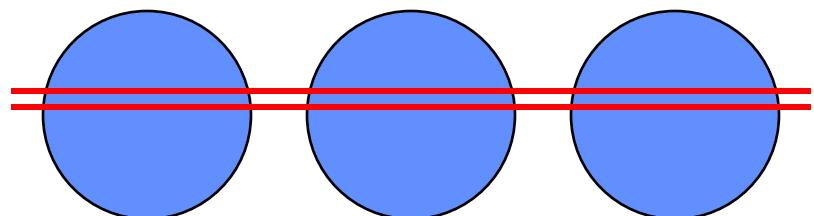
# CdSe quantum dot array, connected by Sn<sub>2</sub>S<sub>6</sub> molecule



Talapin, et.al, Science (2005);  
Kovalenko, et.al, Science (2009).

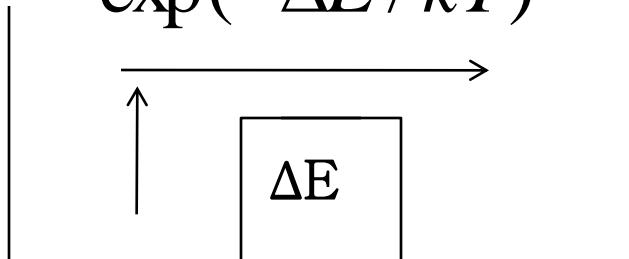
# What cause the electron transport ?

(1) Mini-band bulk like transport:

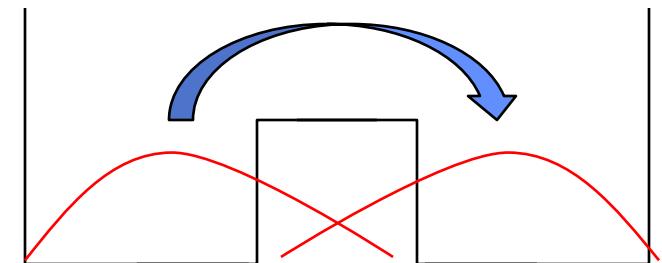


(2) Thermo activation, over the barrier  
(like the Schottky barrier)

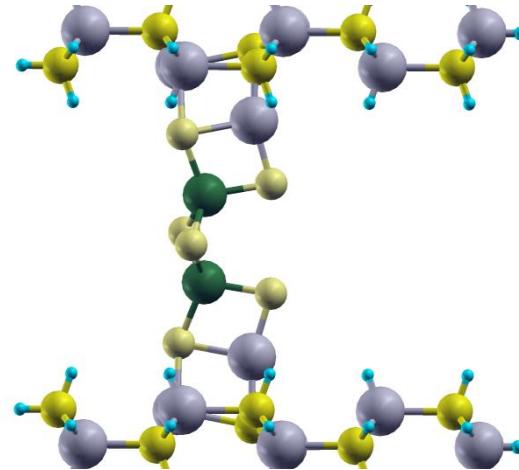
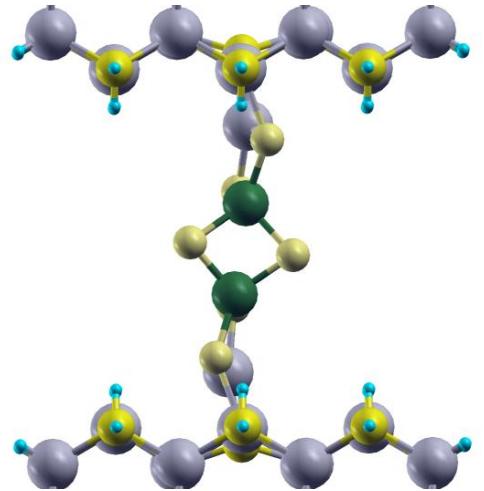
$$\exp(-\Delta E / kT)$$



(3) Phonon assisted hopping  
(e.g., described by Marcus theory)

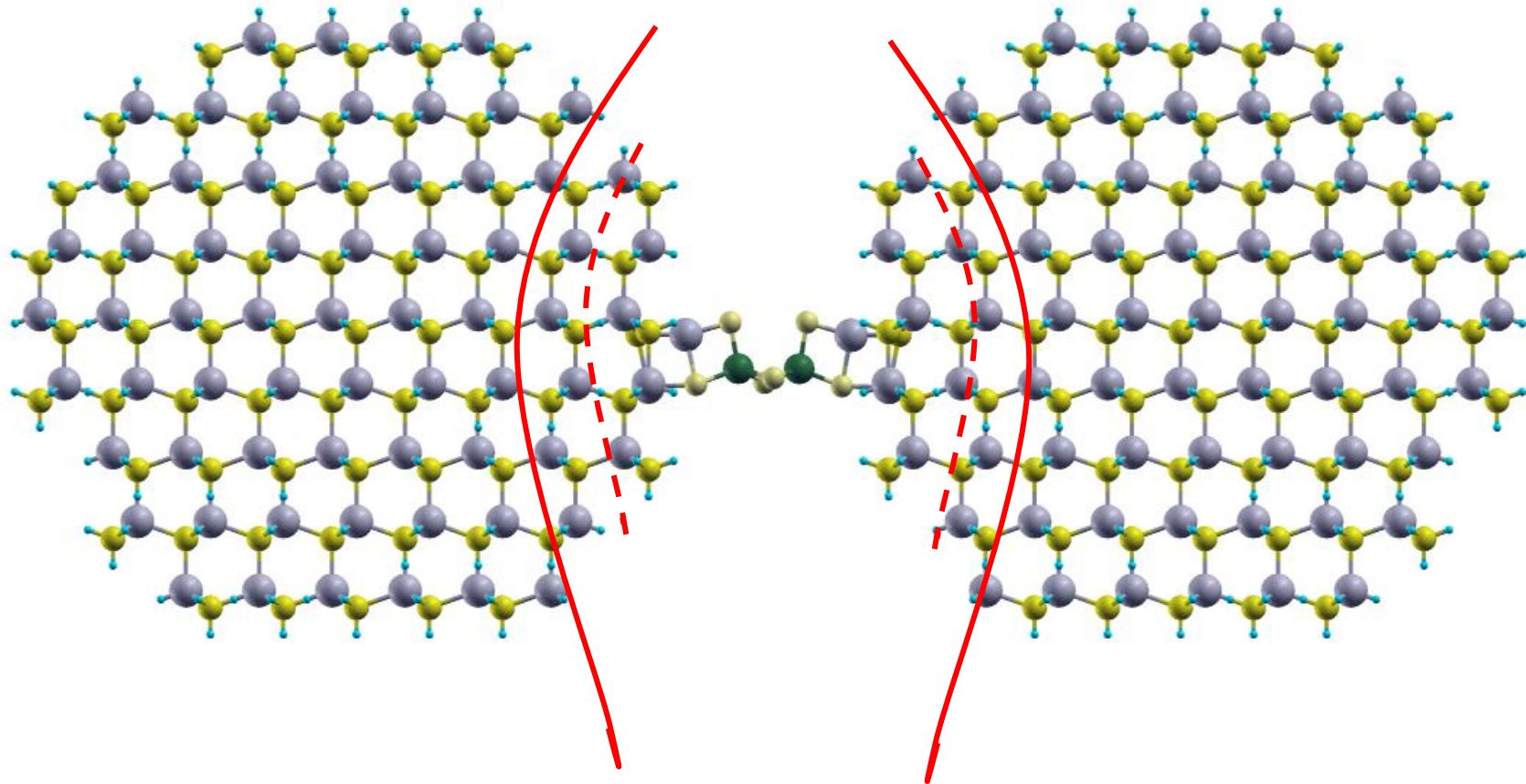


# $\text{Sn}_2\text{S}_6$ atomic attachment to CdSe surfaces

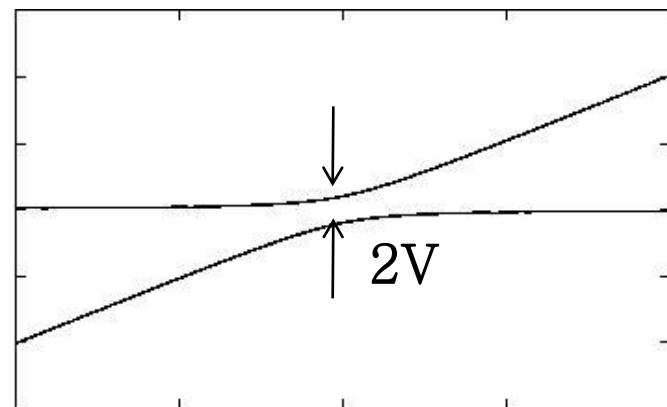
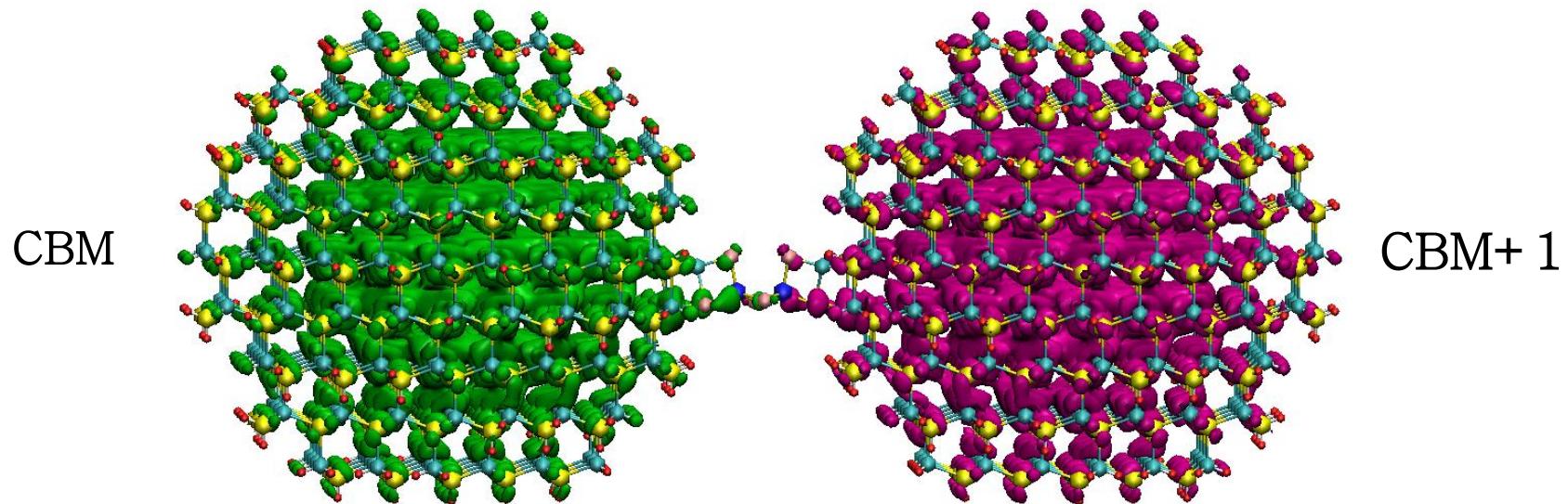


Flat surface calculation for the molecule attachment

# Divide-and-conquer scheme to get the charge density



# The electron coupling between the two states

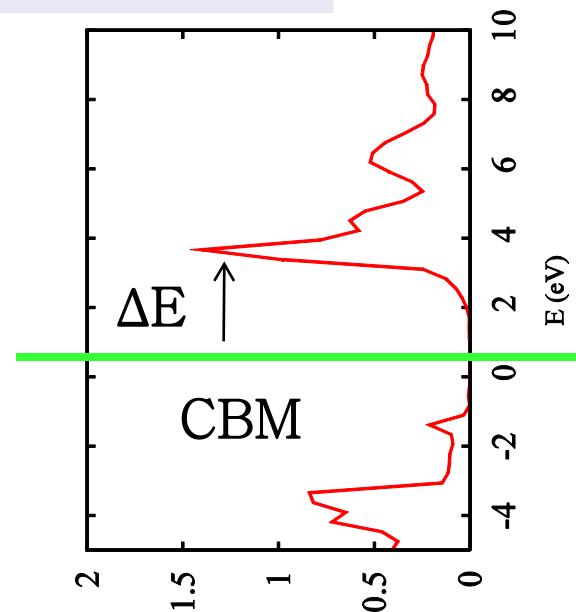


Natom	Size D (nm)	V (coupling meV)
468	2.5	4.1
1051	3.4	1.4
1916	4.3	0.37
3193	5.1	0.14

# Calculating the re-organization energy

Natom	Size D (nm)	$\lambda$ (re-org. energy, meV)	V (coupling meV, type I)
468	2.5	145	4.1
1051	3.4	62	1.4
1916	4.3	32	0.37
3193	5.1	23	0.14

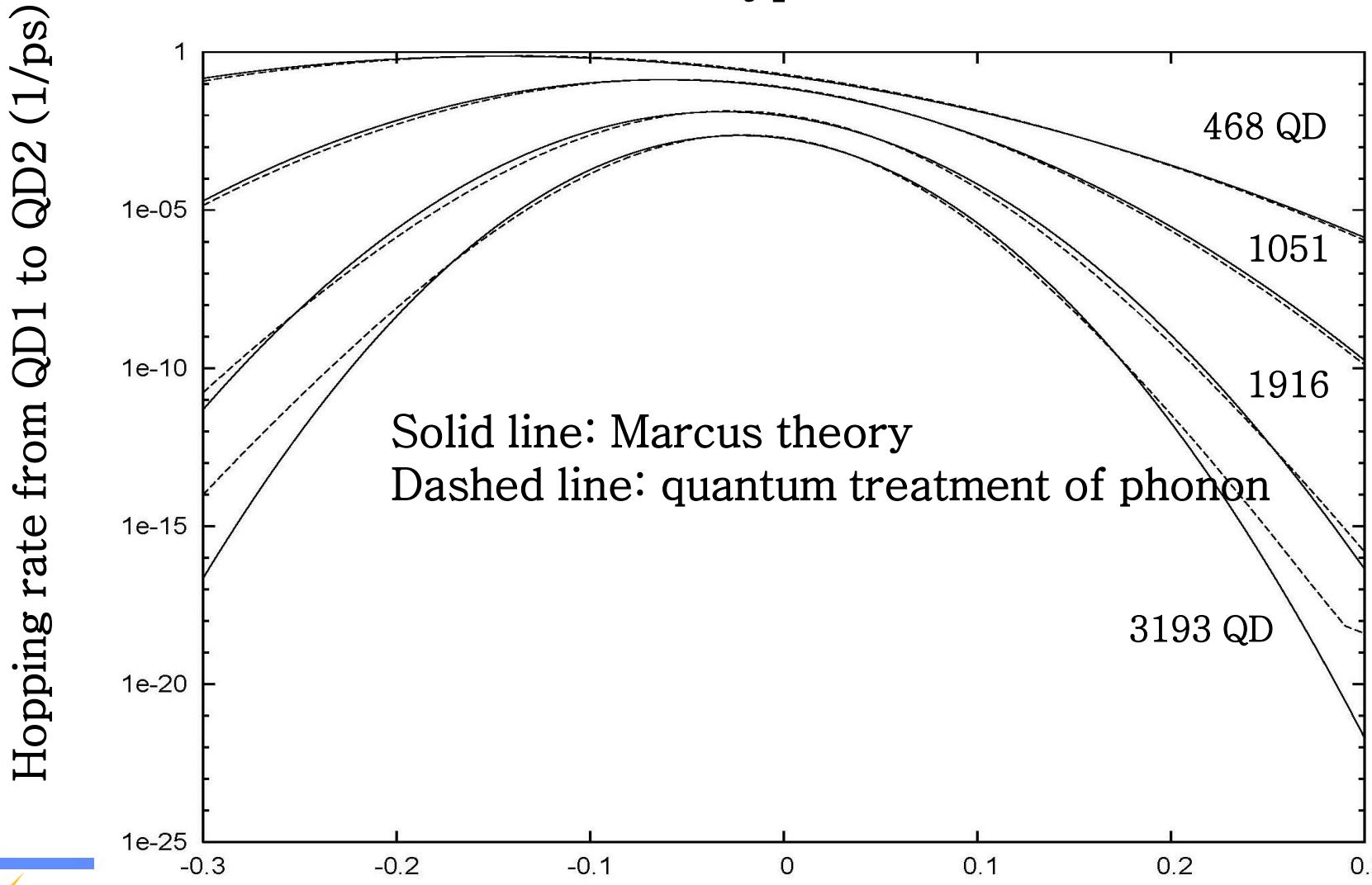
- (1) The  $\lambda \gg V$ , so the wave function will be localized, it is not mini-band transport
- (2) the barrier height  $\Delta E$  can be  $\sim 2$  eV.  
It cannot be over-the-barrier thermally excited transport.
- (3) Must be phonon-assisted hopping transport



LDOS

# The hopping rate

## Attachment type I



# Carrier mobility of the QD array in small carrier density limit

Situation (QD cubic array, size=4.3nm)	Type-I attachment Mobility $\mu$ (cm $^2$ /V/S)
No QD size fluctuation, no connection fluctuation	$8.22 \times 10^{-2}$
5% QD size fluctuation, no connection fluctuation	$4.80 \times 10^{-2}$
5% QD size fluctuation, uniform connection fluctuation	$1.02 \times 10^{-2}$
Experiment, size=4.5nm	$3 \times 10^{-2}$

# Why are quantum mechanical calculations so expensive?

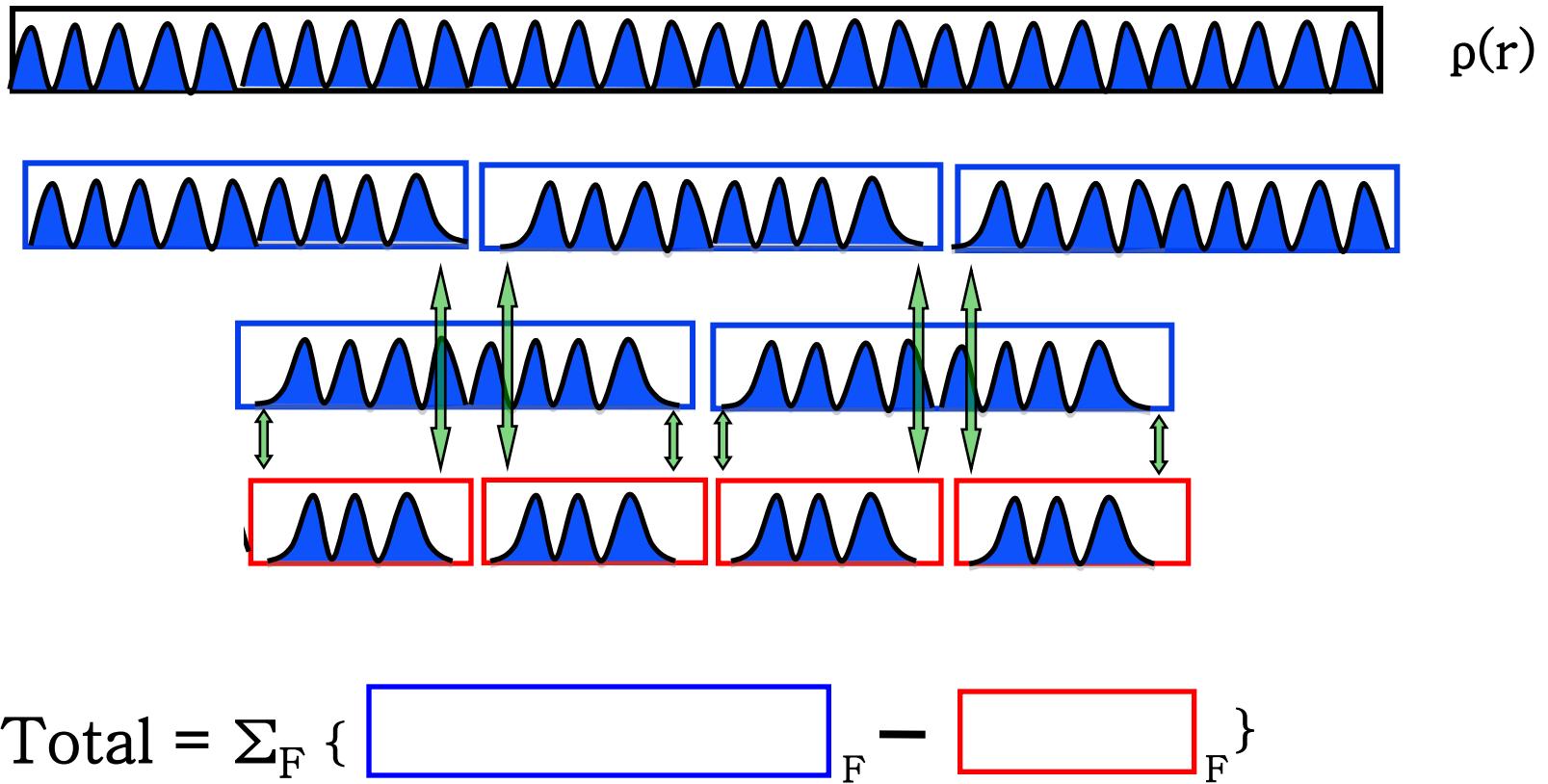


$$\left[ -\frac{1}{2} \nabla^2 + V_{tot}(r) \right] \psi_i(r) = \epsilon_i \psi_i(r)$$

- ◆ If the size of the system is  $N$ :
- ◆  $N$  coefficients to describe one wavefunction  $\psi_i(r)$
- ◆  $i = 1, \dots, M$  wavefunctions  $\psi_i(r)$ ,  $M$  is proportional to  $N$ .
- ◆ Orthogonalization:  $M^2$  wavefunction pairs  $\int \psi_i(r) \psi_j^*(r) d^3r$  each with  $N$  coefficients:  $N^*M^2$ , i.e.  $N^3$  scaling.

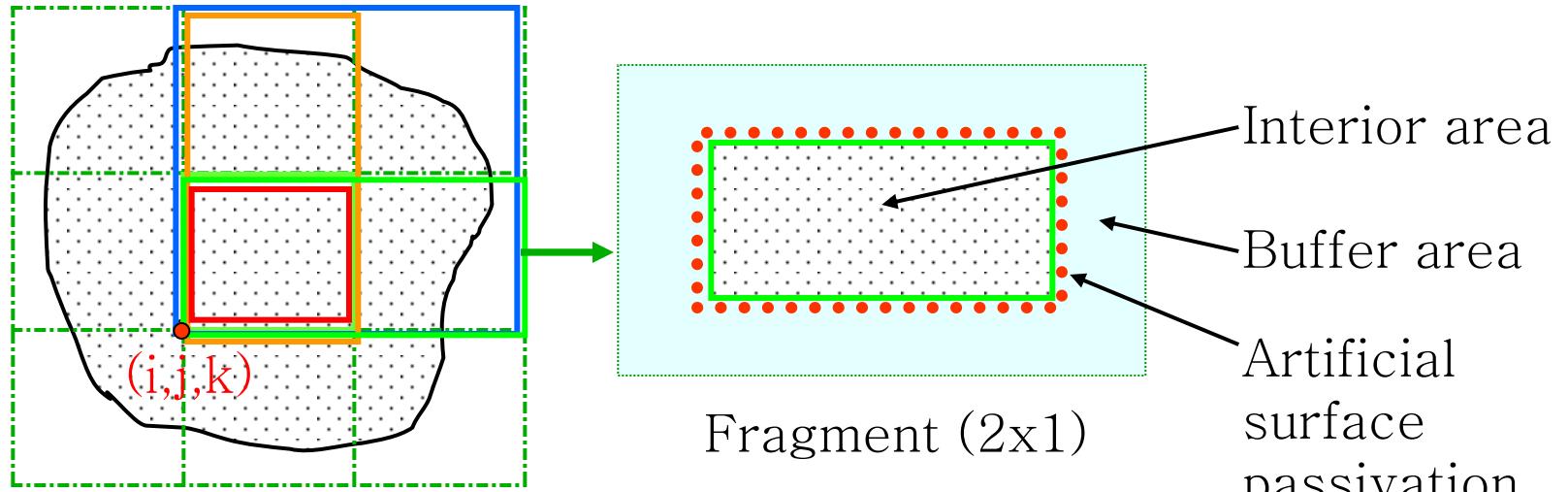
The repeated calculation of these orthogonal wavefunctions make the computation expensive,  $O(N^3)$ . For large systems, an  $O(N)$  method is critical

# LS3DF: 1D Example



Phys. Rev. B 77, 165113 (2008); J. Phys: Cond. Matt. 20, 294203 (2008)

## Similar procedure extends to 2 and 3D



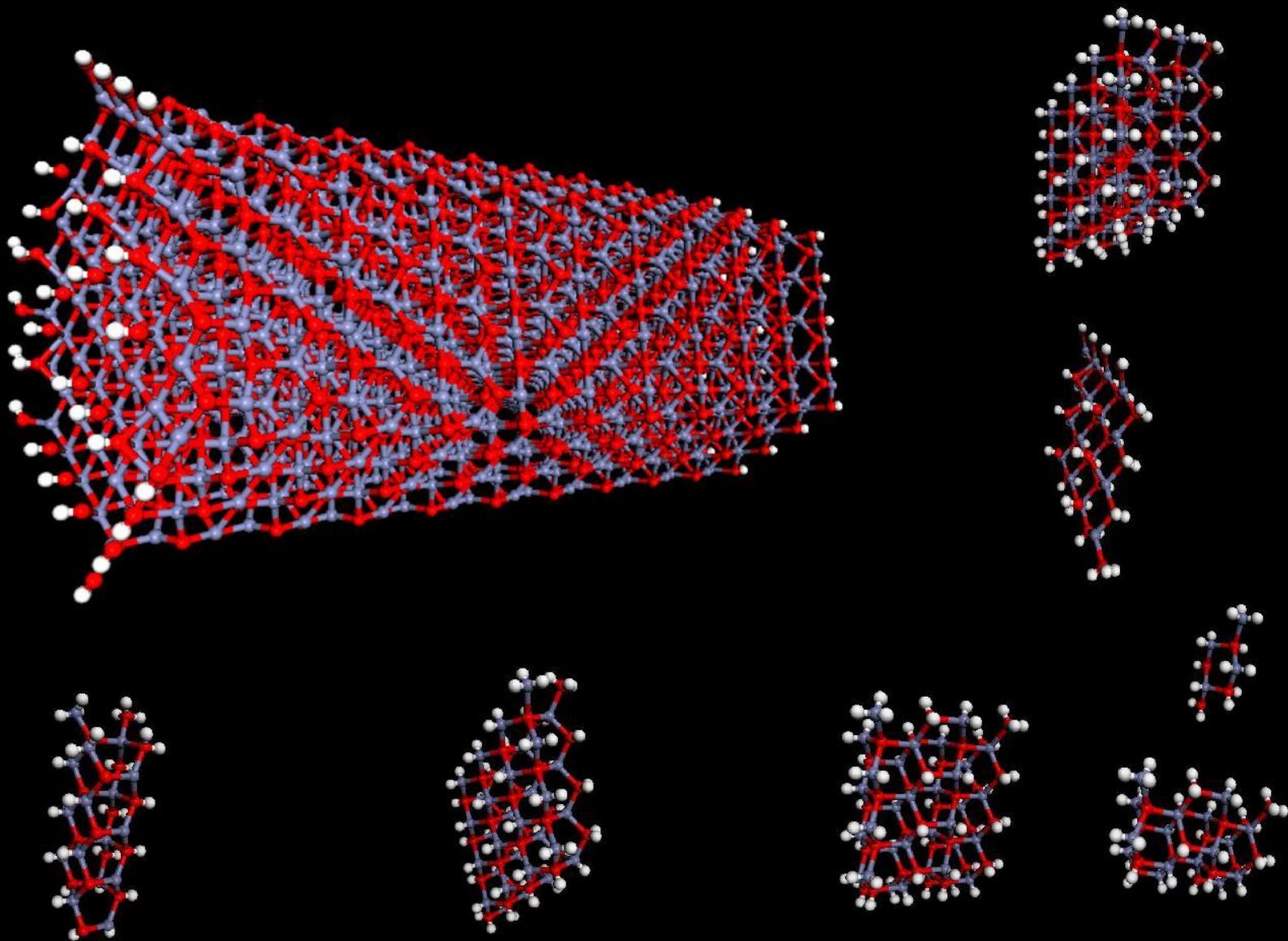
Fragment (2x1)

$$\text{Total} = \sum_F \{ \text{[Blue Box]} - \text{[Orange Box]} - \text{[Green Box]}_F + \text{[Red Box]}_F \}$$

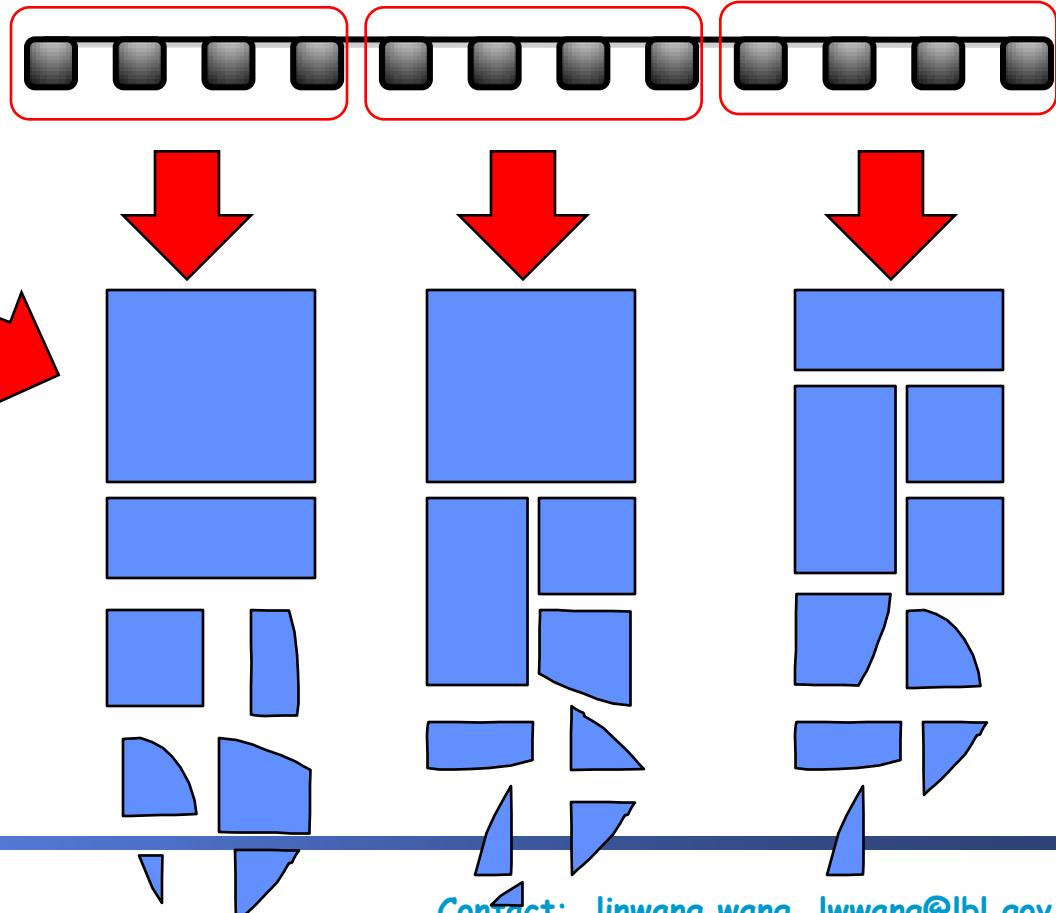
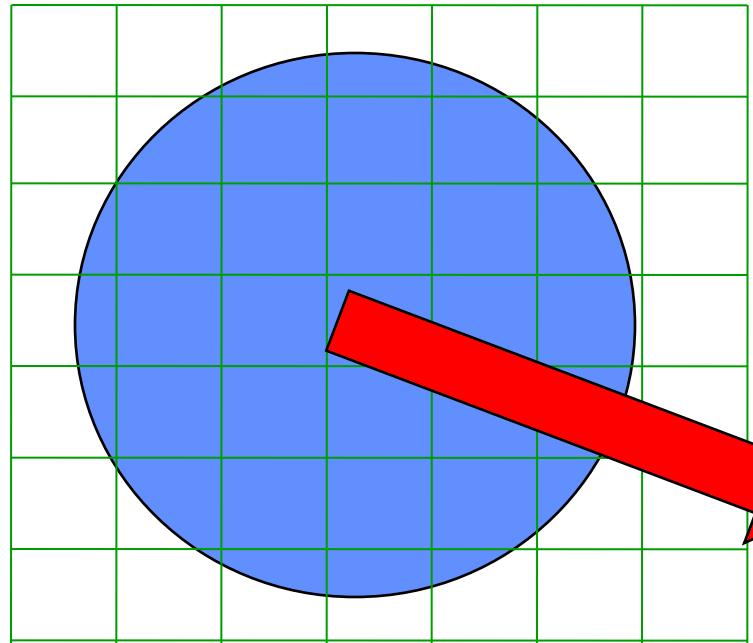
Boundary effects are (nearly) cancelled out between the fragments

$$\text{System} = \sum_{i,j,k} \{ F_{222} + F_{211} + F_{121} + F_{112} - F_{221} - F_{212} - F_{122} - F_{111} \}$$

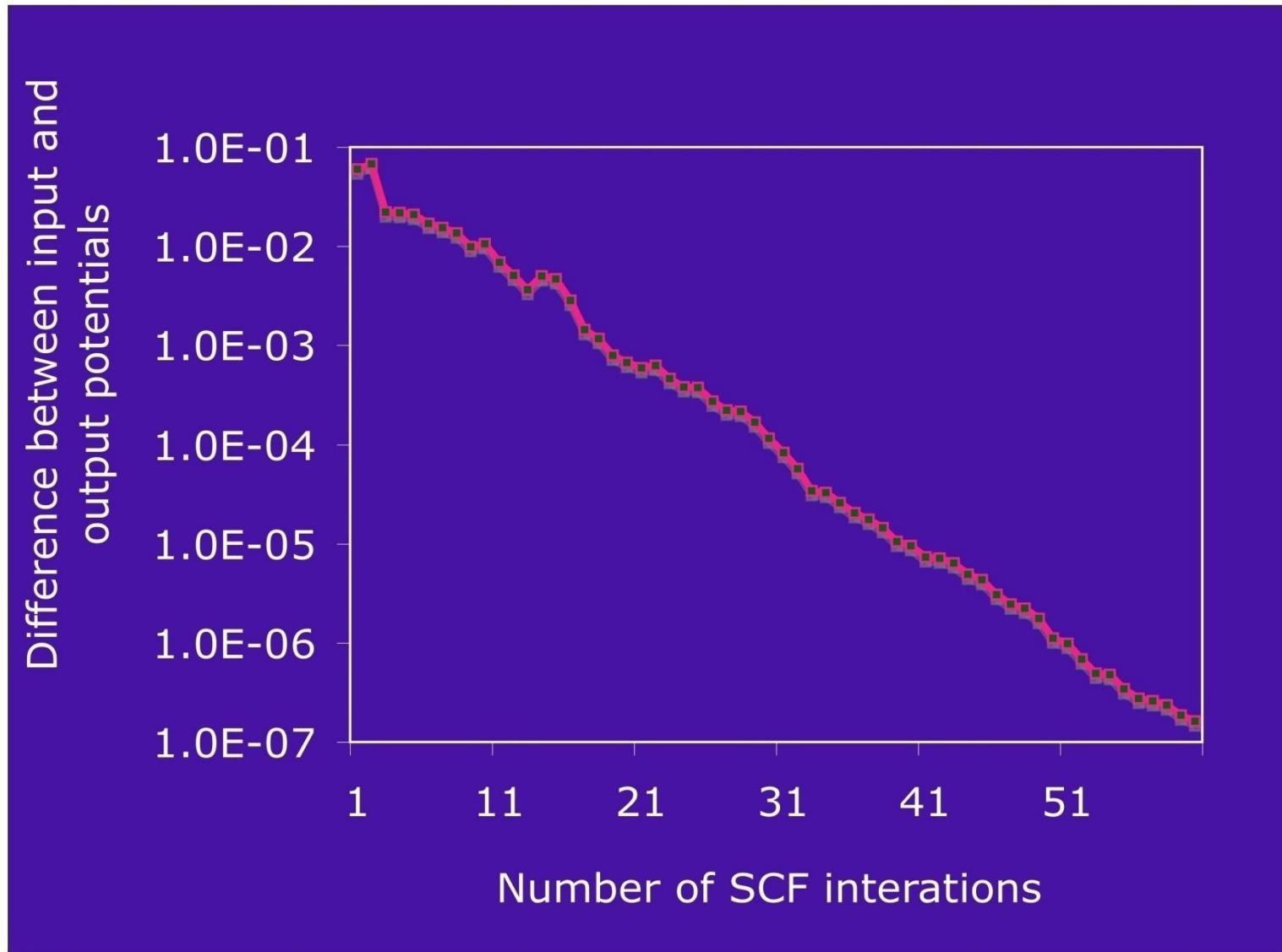
# A example of the global system and the fragments



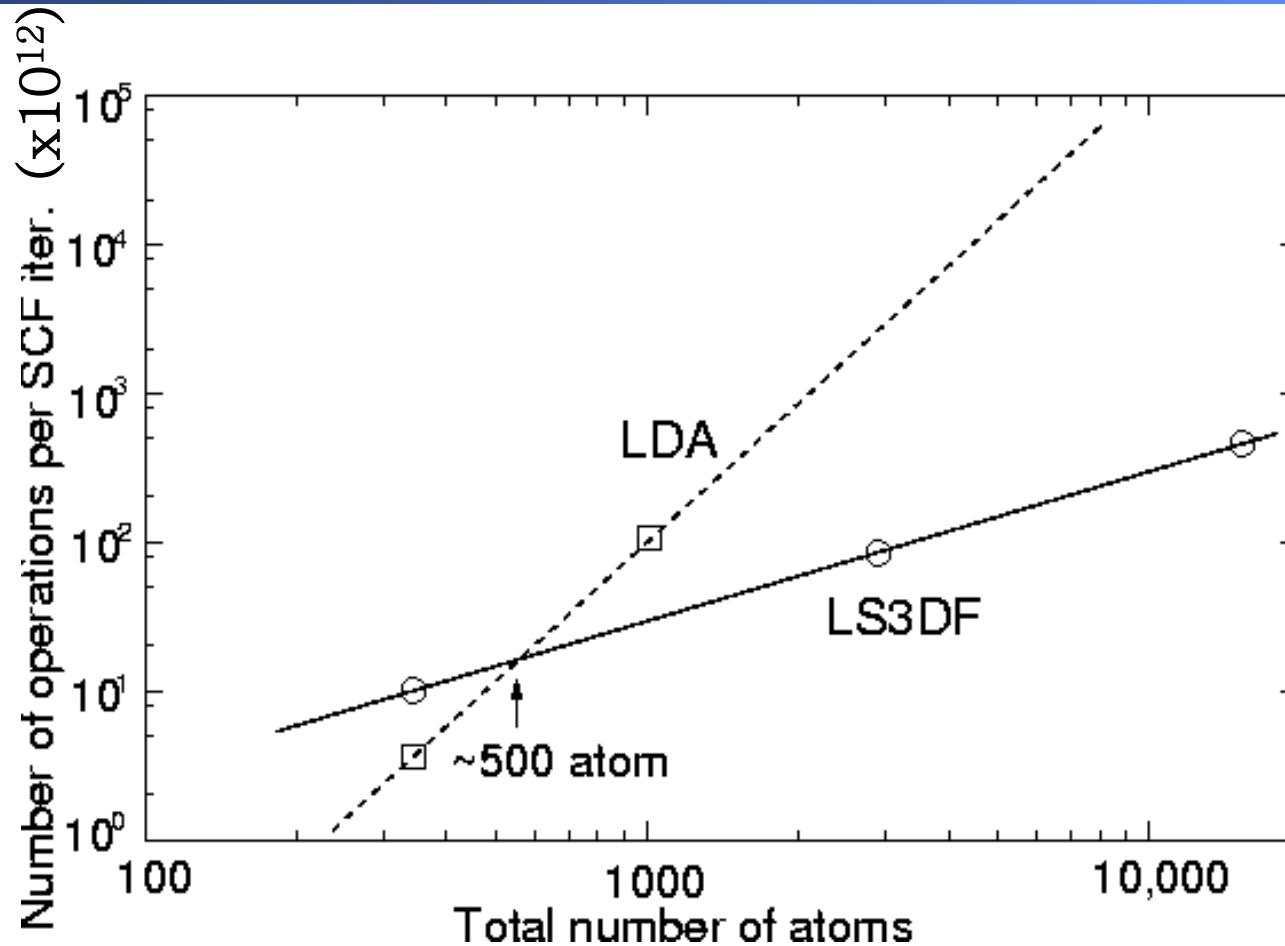
# Schematics for LS3DF calculation



# No selfconsistent problem for the global system



# Operation counts

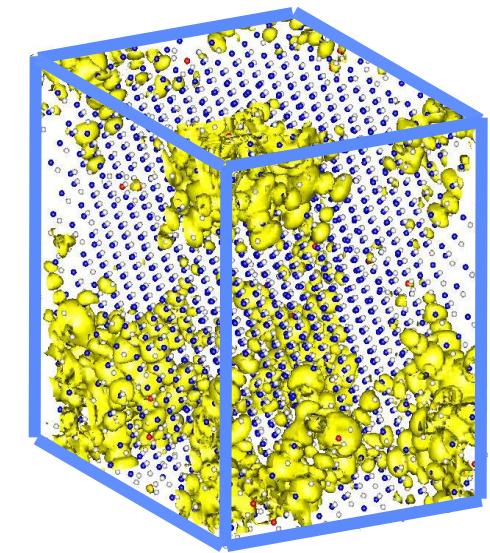
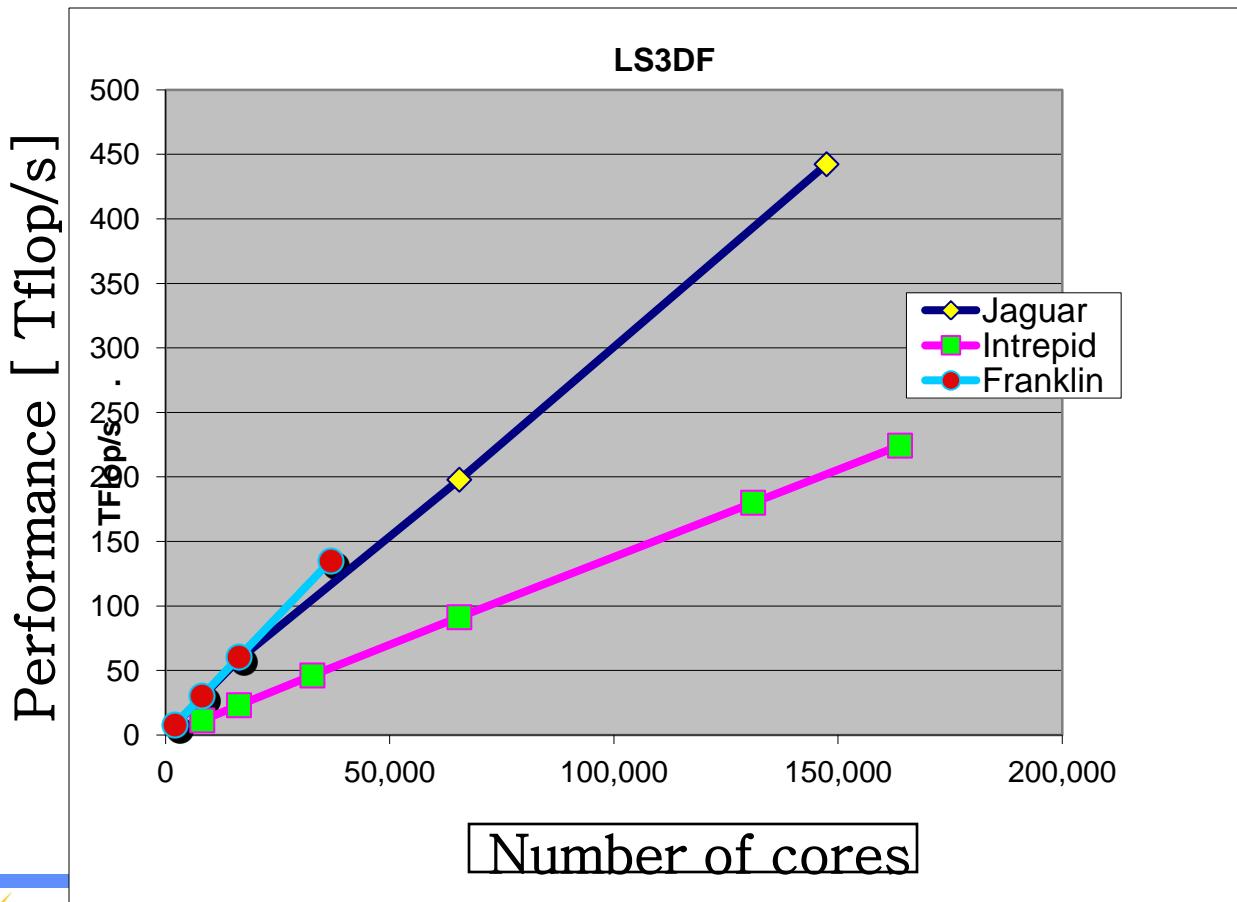


- ❖ Cross over with direct LDA method [PEtot] is 500 atoms.
- ❖ Similar to other  $O(N)$  methods.

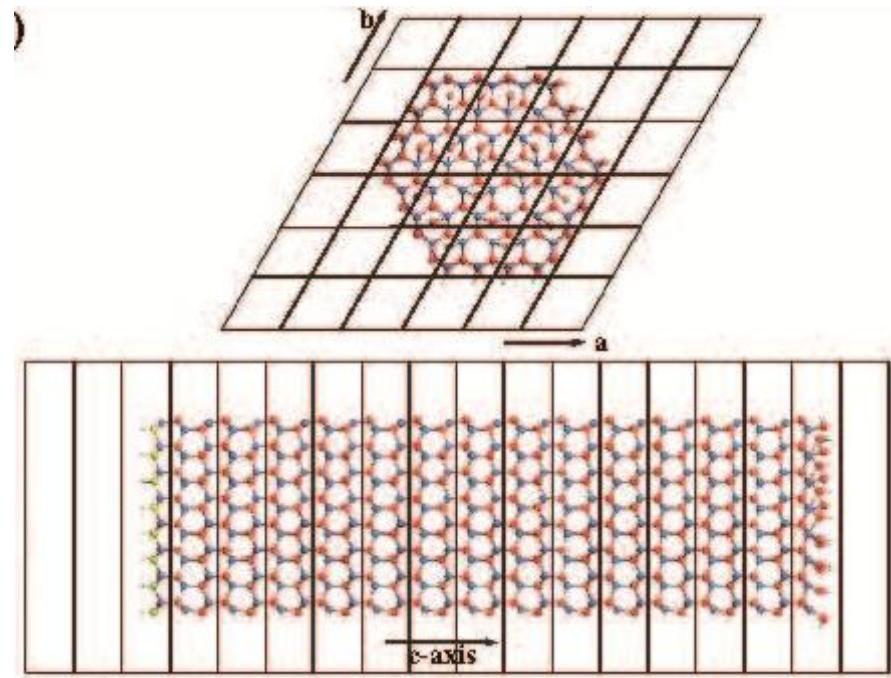
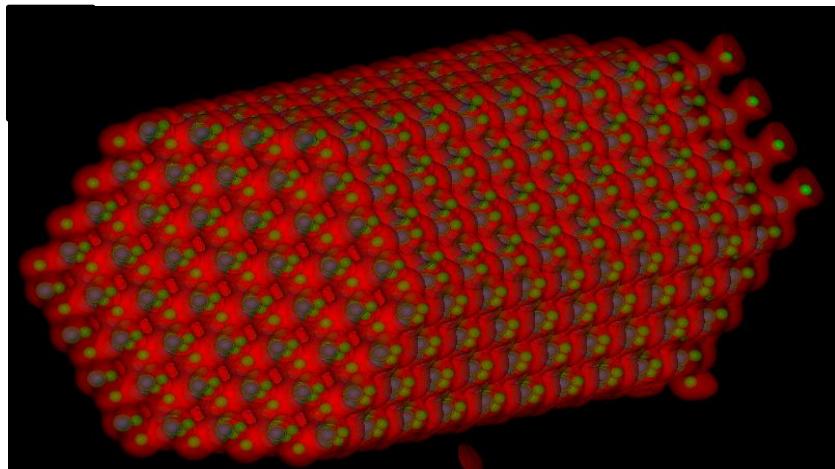
# ZnTeO alloy weak scaling calculations



- First large scale run on Franklin at NERSC: 135 Tflops/s, 40% efficiency
- Subsequent runs on Intrepid at ALCF: 224 Tflops/s, 40% efficiency
- Final runs on Jaguar XT5 at NCCS: 442 Tflops/s, 33% efficiency



# A more detail example of the ZnO nanorod system



Num atom: 2776

Num electron: 24220

Real space grid: 720x300x300

Fragment dividing grid: 18x6x6

# Conclusion

